

Computer Architecture
Computer Engineering Track
Optional Tutorial 6

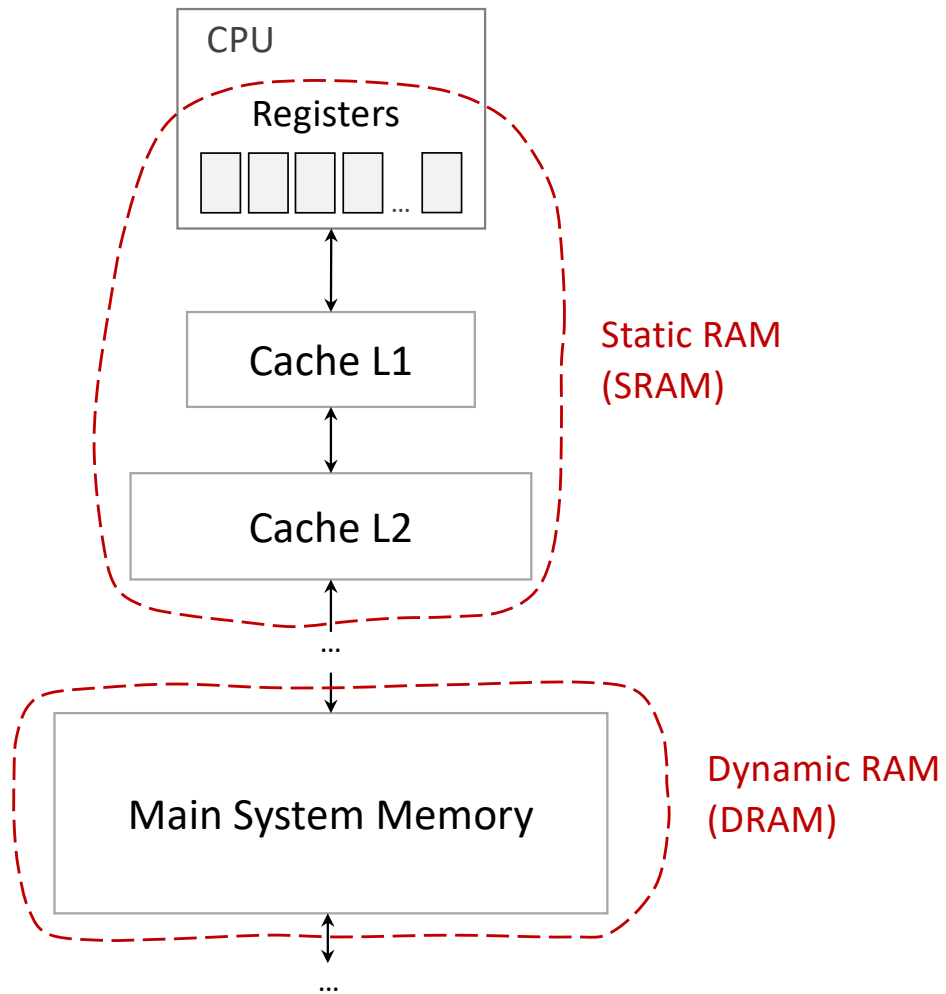
The Revision of Selected Topics:
SRAM and DRAM
Latches

Artem Burmyakov, Muhammad Fahim, Alexander Tormasov

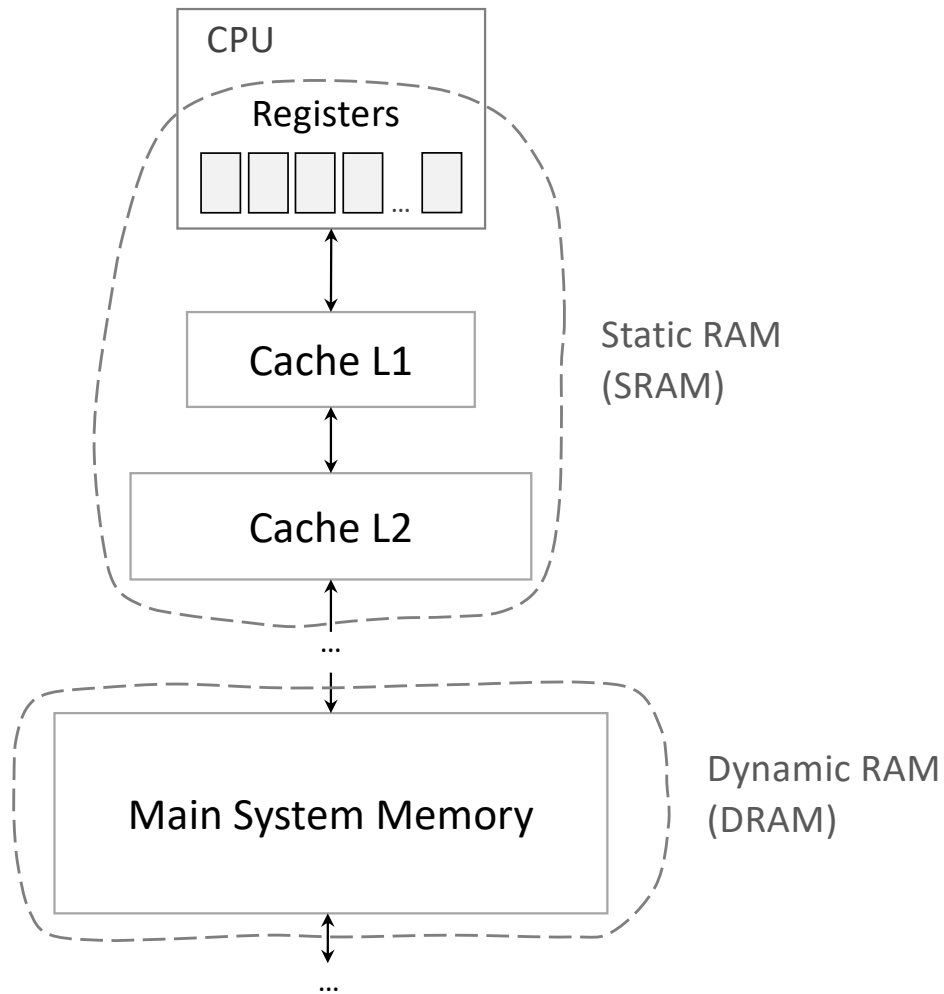
October 09, 2020



Memory Hierarchy – the Fundamental Idea of Computer Architecture

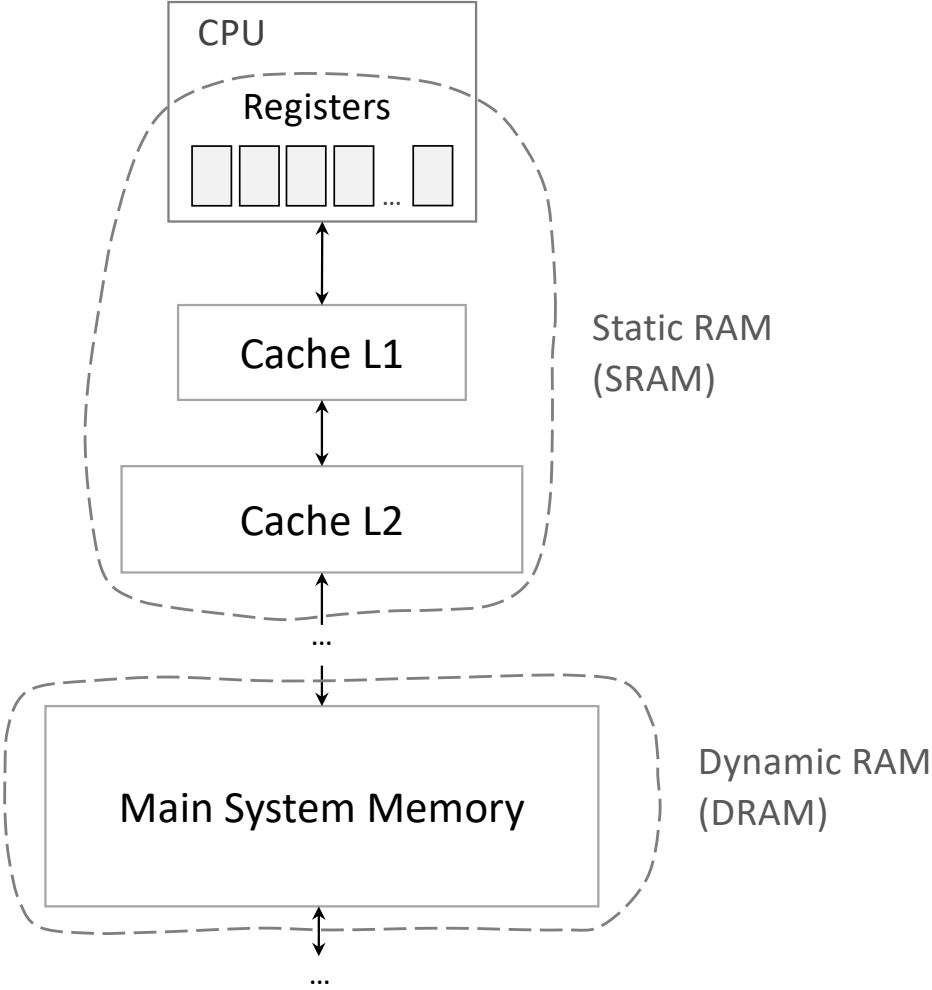


The Comparison of DRAM and SRAM Memory Types



Characteristic	SRAM	DRAM
Access Speed	Faster	Slower
Storage Capacity	Smaller	Larger
Storage Element	Flip-flop (Latch)	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption	Lower	Higher
Organisation	Complex	Simpler
Power Leakage	Not present	Significant
Chip Reliability	More reliable	Less reliable
Volatility	Both are volatile (require electrical power to keep data)	
Memory Cell Access	Each cell is accessed directly, unlike Sequential Access Memory (SAM)	

The Comparison of DRAM and SRAM Memory Types

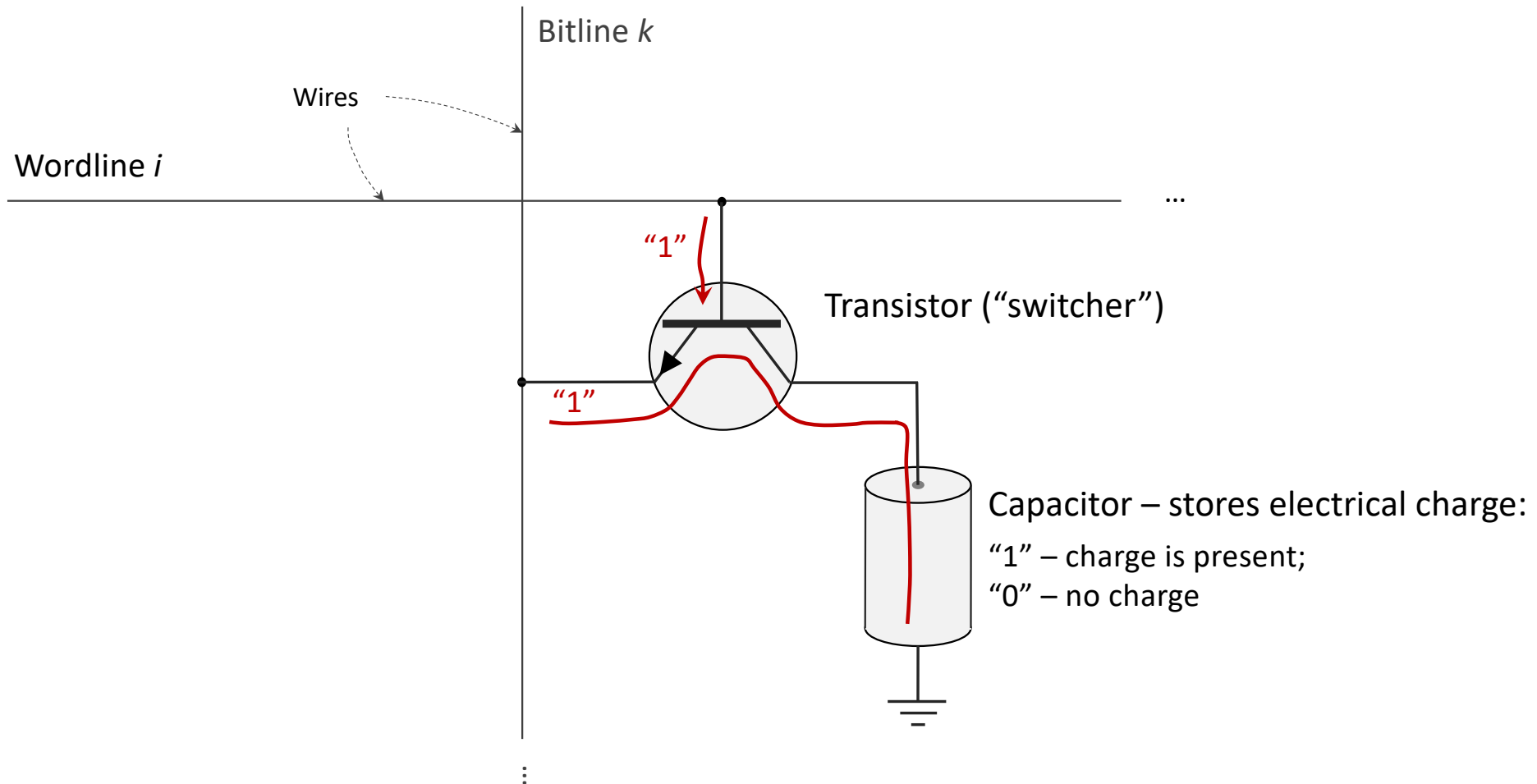


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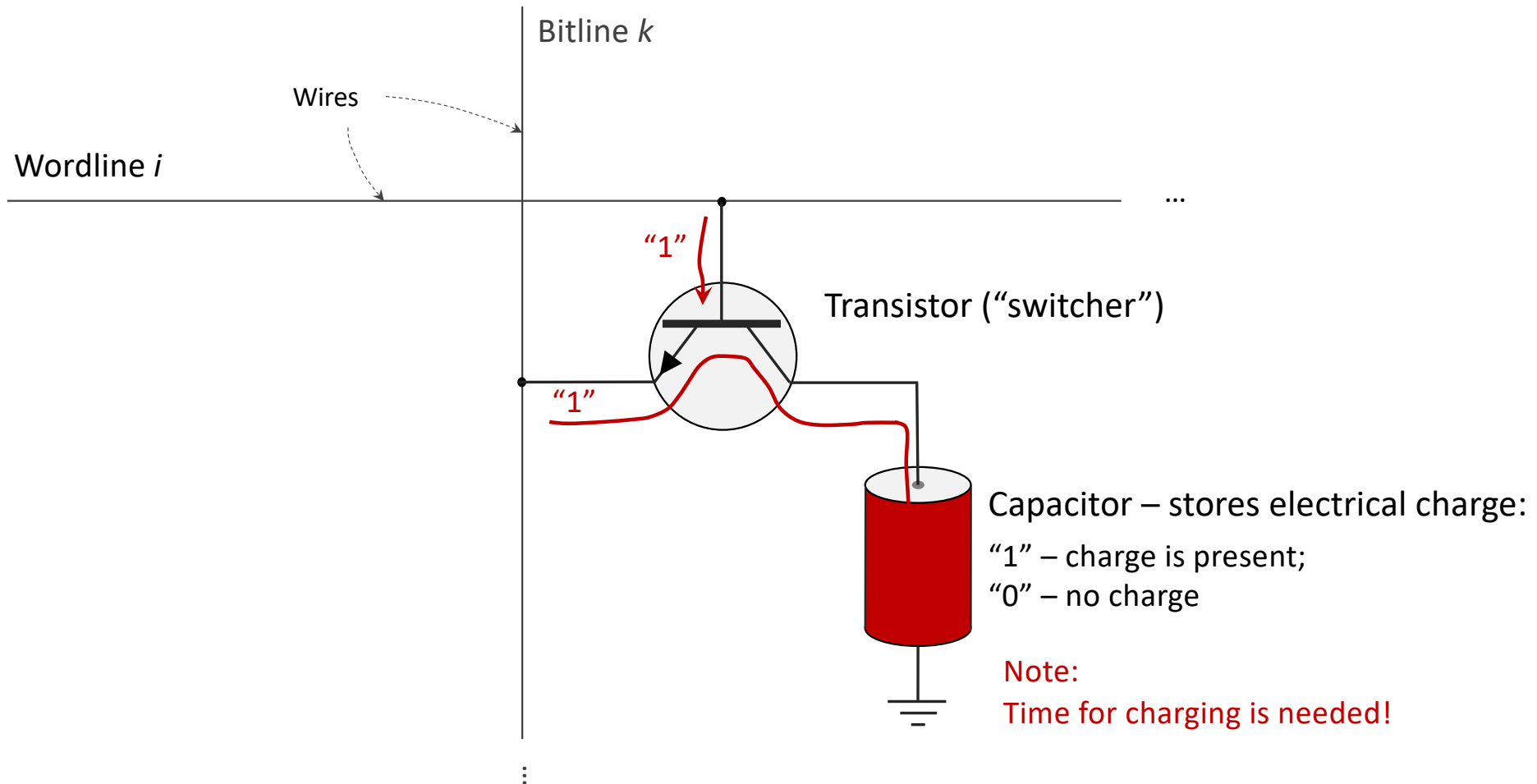
Capacitor: a physical device to store electrical charge



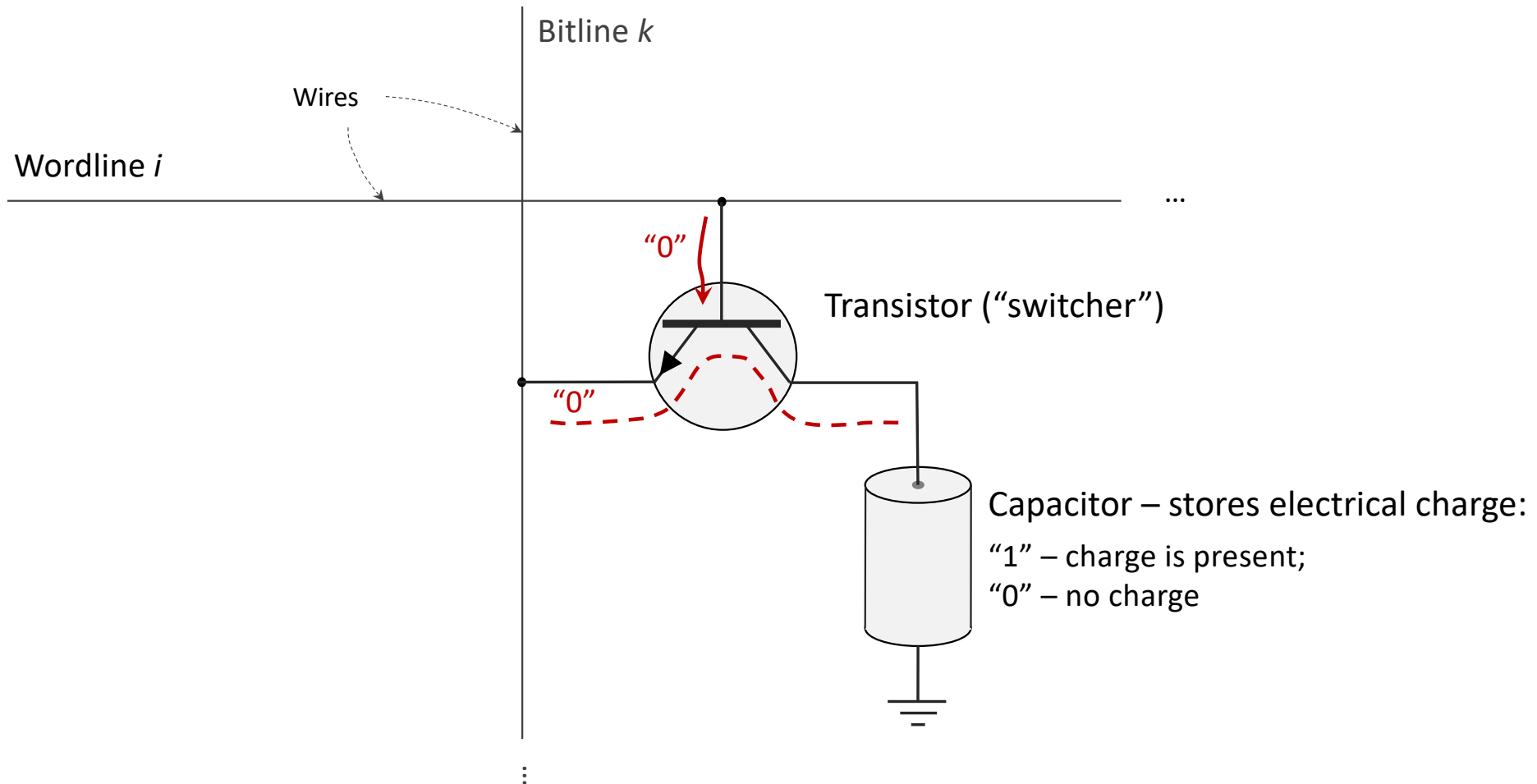
DRAM memory cell



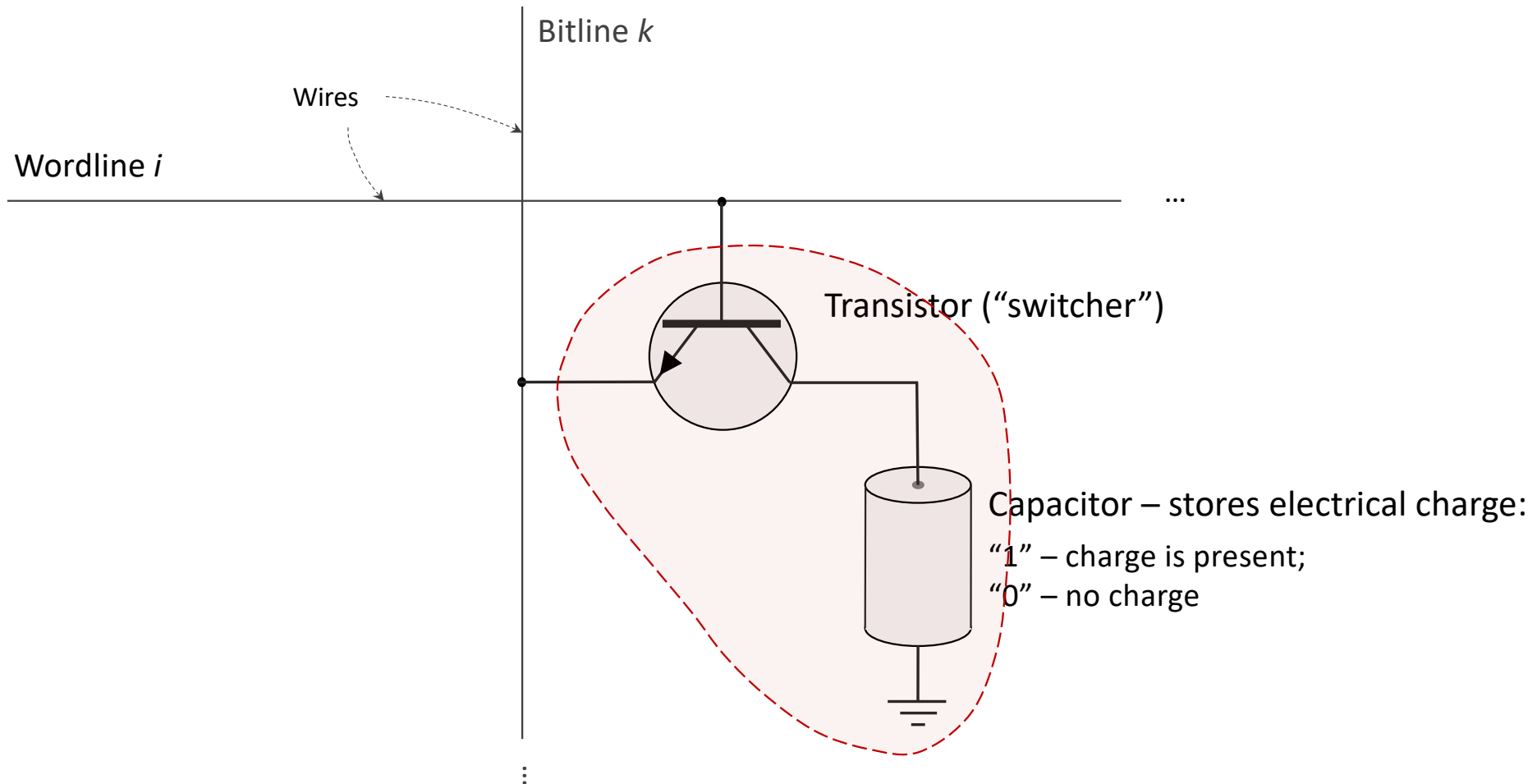
DRAM memory cell



DRAM memory cell



DRAM memory cell



DRAM memory cell: capacitor + transistor

DRAM memory cell

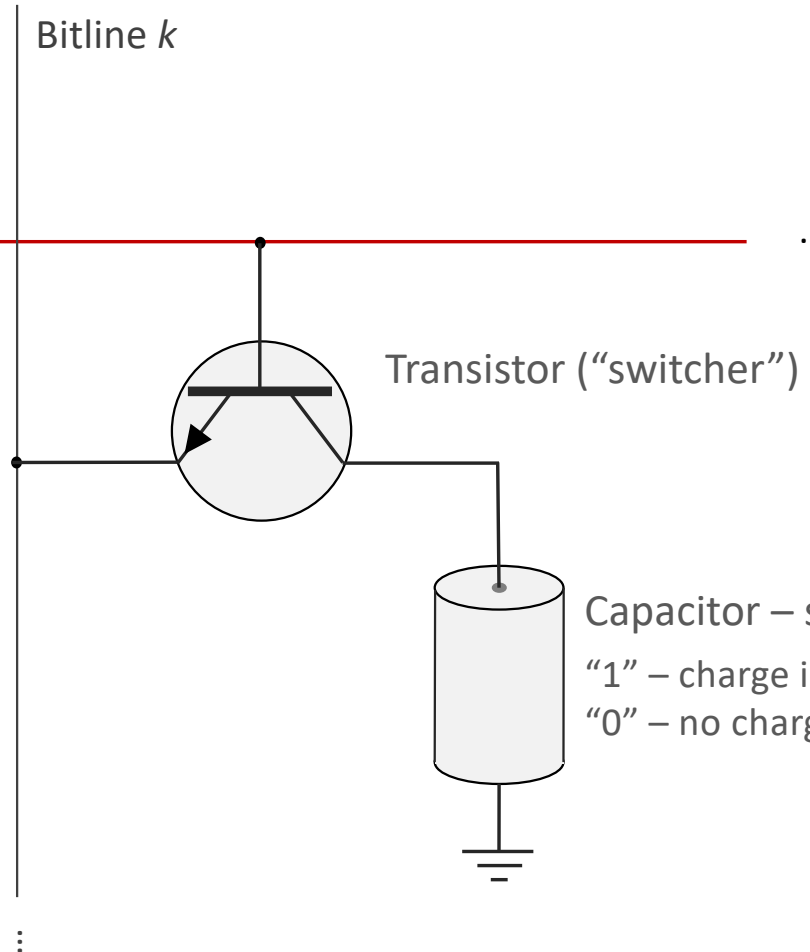
Wordline i

activates memory cell
for read/write operations:

Input "1" – line selected for operation,
and thus, transistor is "ON";

Input "0" – line is deactivated

Bitline k



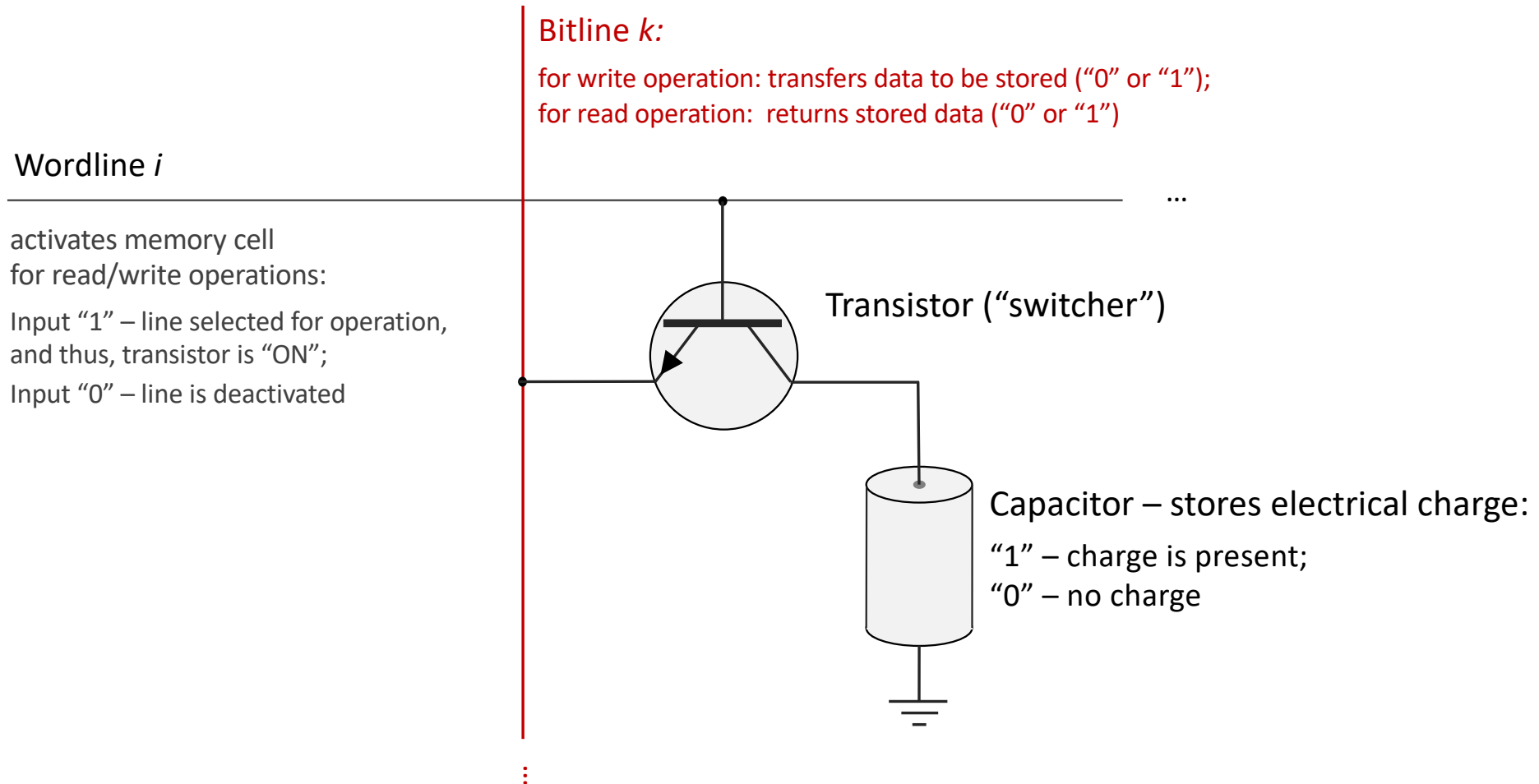
Transistor ("switcher")

Capacitor – stores electrical charge:

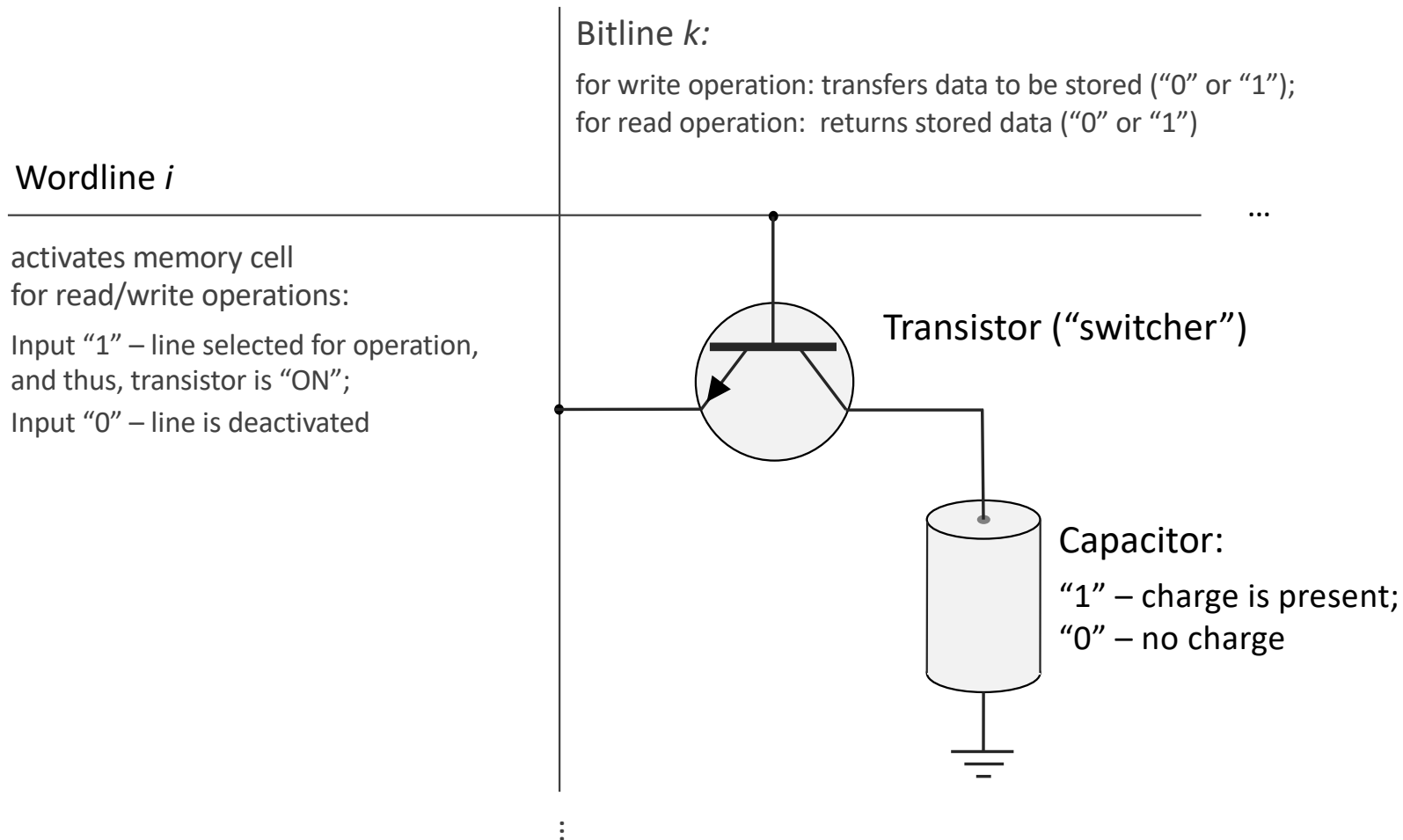
"1" – charge is present;

"0" – no charge

DRAM memory cell



Writing into DRAM memory cell



Writing into DRAM memory cell

1) Activation of the wordline,
corresponding to the address of a
memory cell;

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Bitline k :

for write operation: transfers data to be stored ("0" or "1");

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"1"

Transistor ("switcher")

Capacitor:

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⋮

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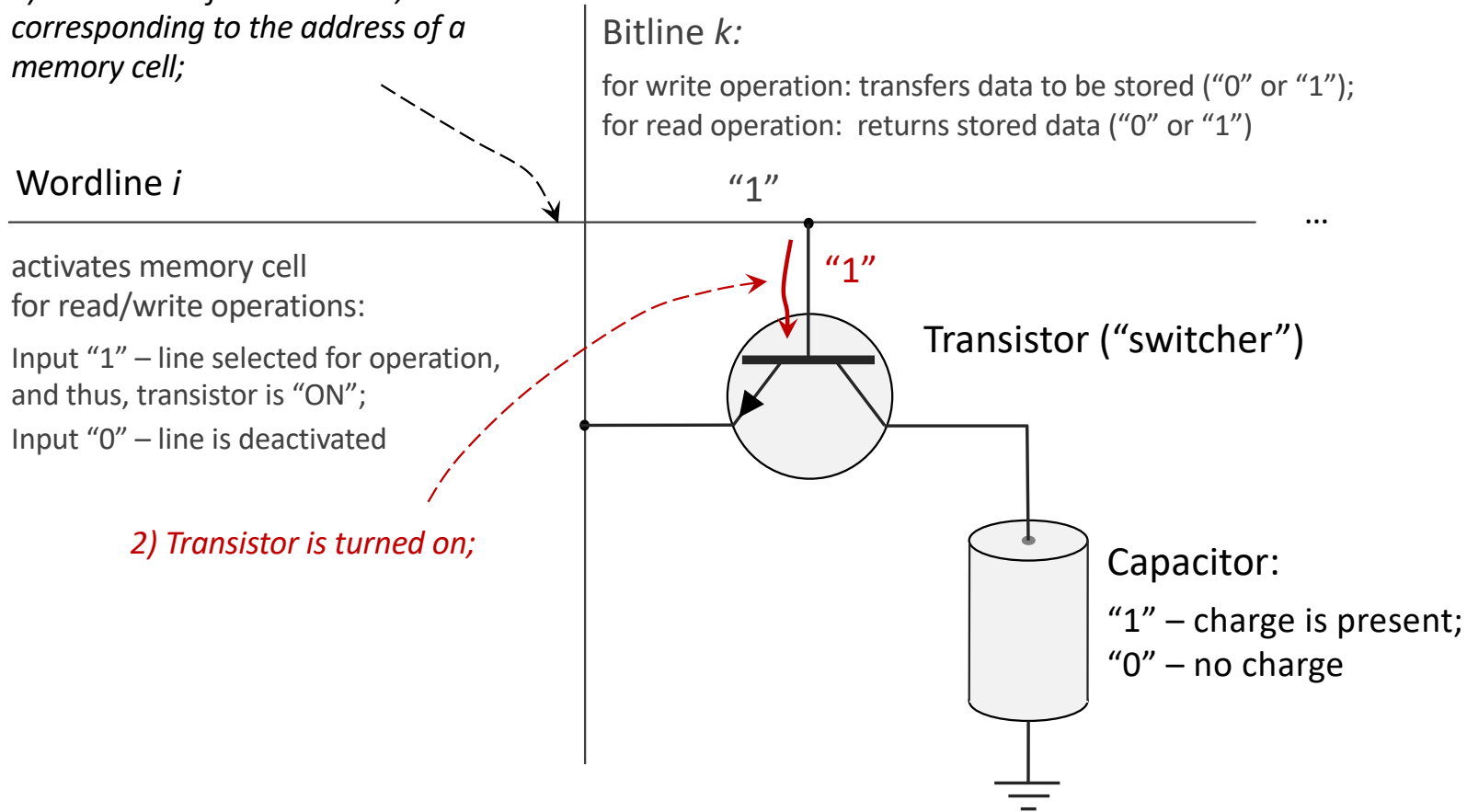
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"1"

Transistor ("switcher")

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"1"

Capacitor:

"1" – charge is present;

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3) Transferring data bit over the bitline, to be stored;

If "1" – capacitor gets charged (however, some time for charging is needed)

Writing into DRAM memory cell

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"1"

Transistor ("switcher")

"0"

discharging

Capacitor:

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"0"

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Else if "0" – capacitor is discharged

Writing into DRAM memory cell

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"1"

"1"

Transistor ("switcher")

"0"

"0"

Capacitor:

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Reading from DRAM memory cell

1) *Activation of the wordline, corresponding to the address of a memory cell;*

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"1"

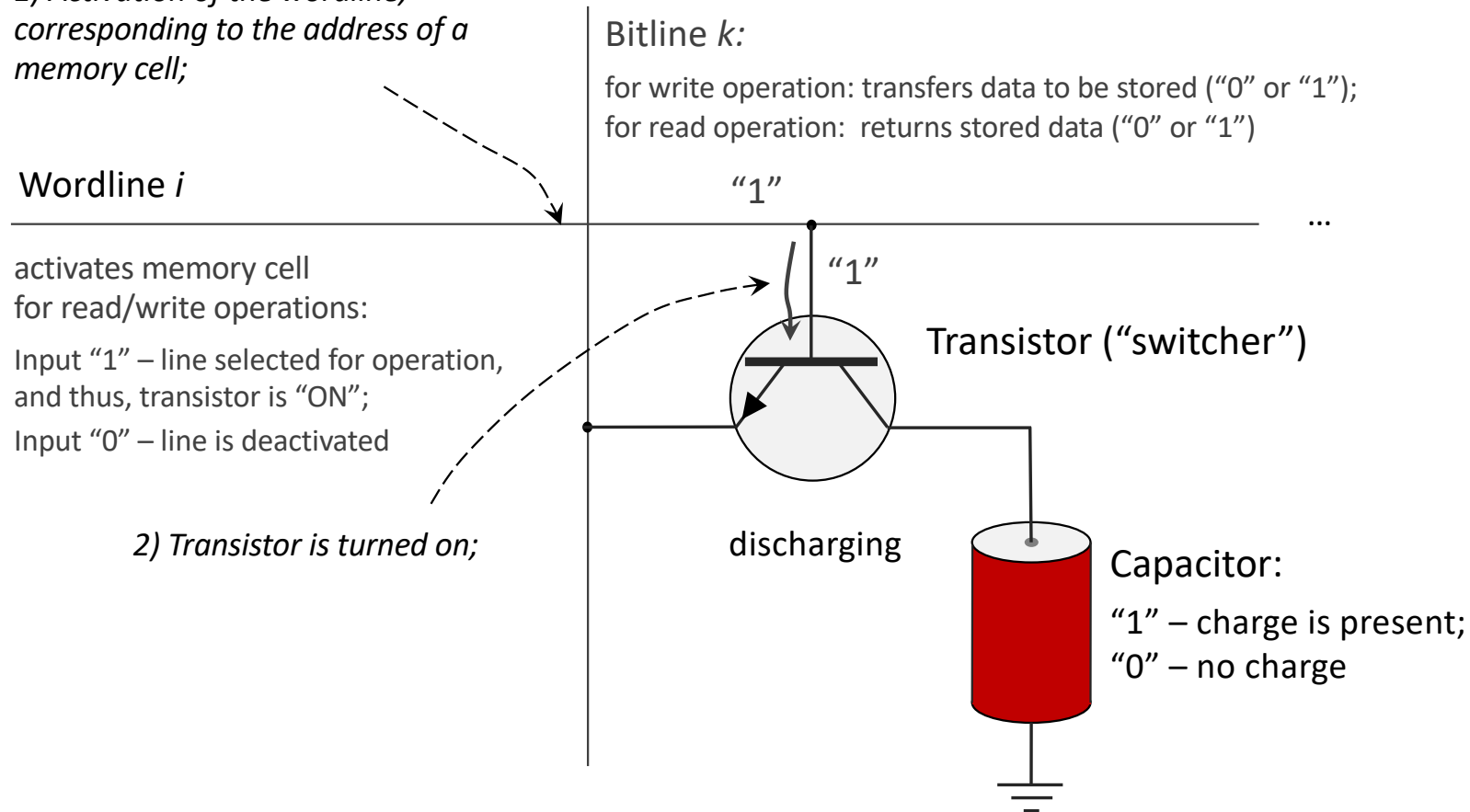
Transistor ("switcher")

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Reading from DRAM memory cell

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Transistor ("switcher")

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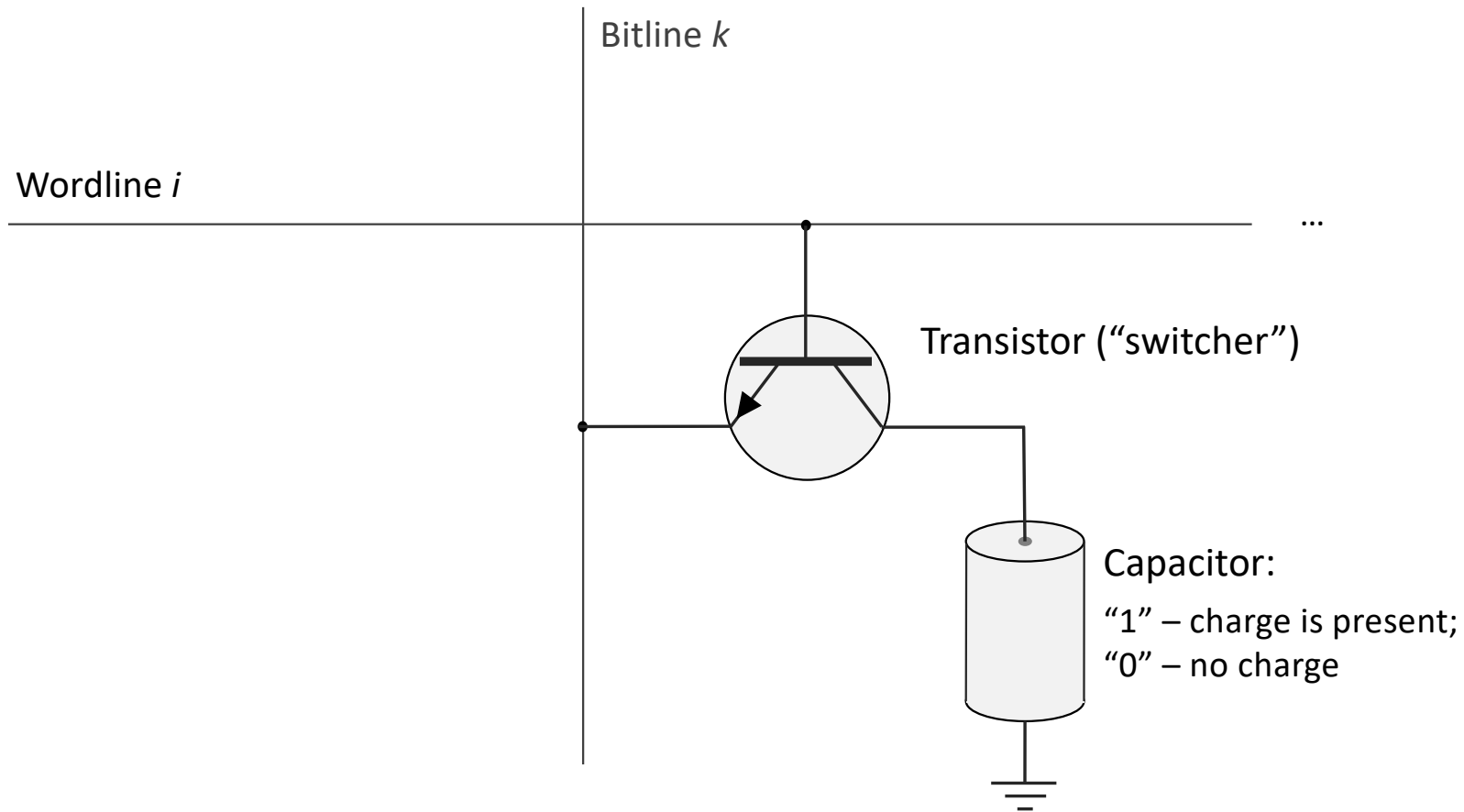
Capacitor:

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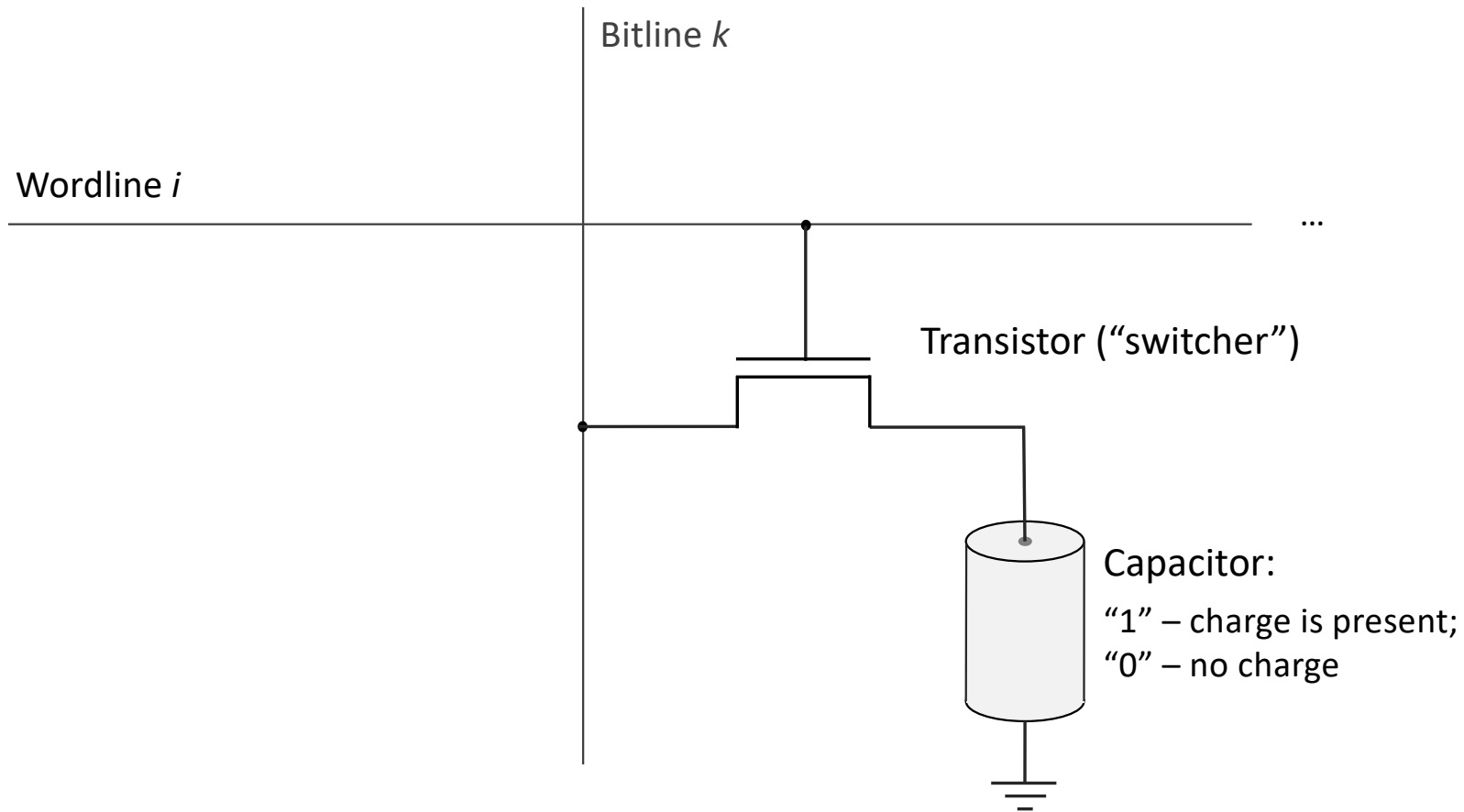
"0" – no charge

3) Transferring data bit from capacitor over the bitline

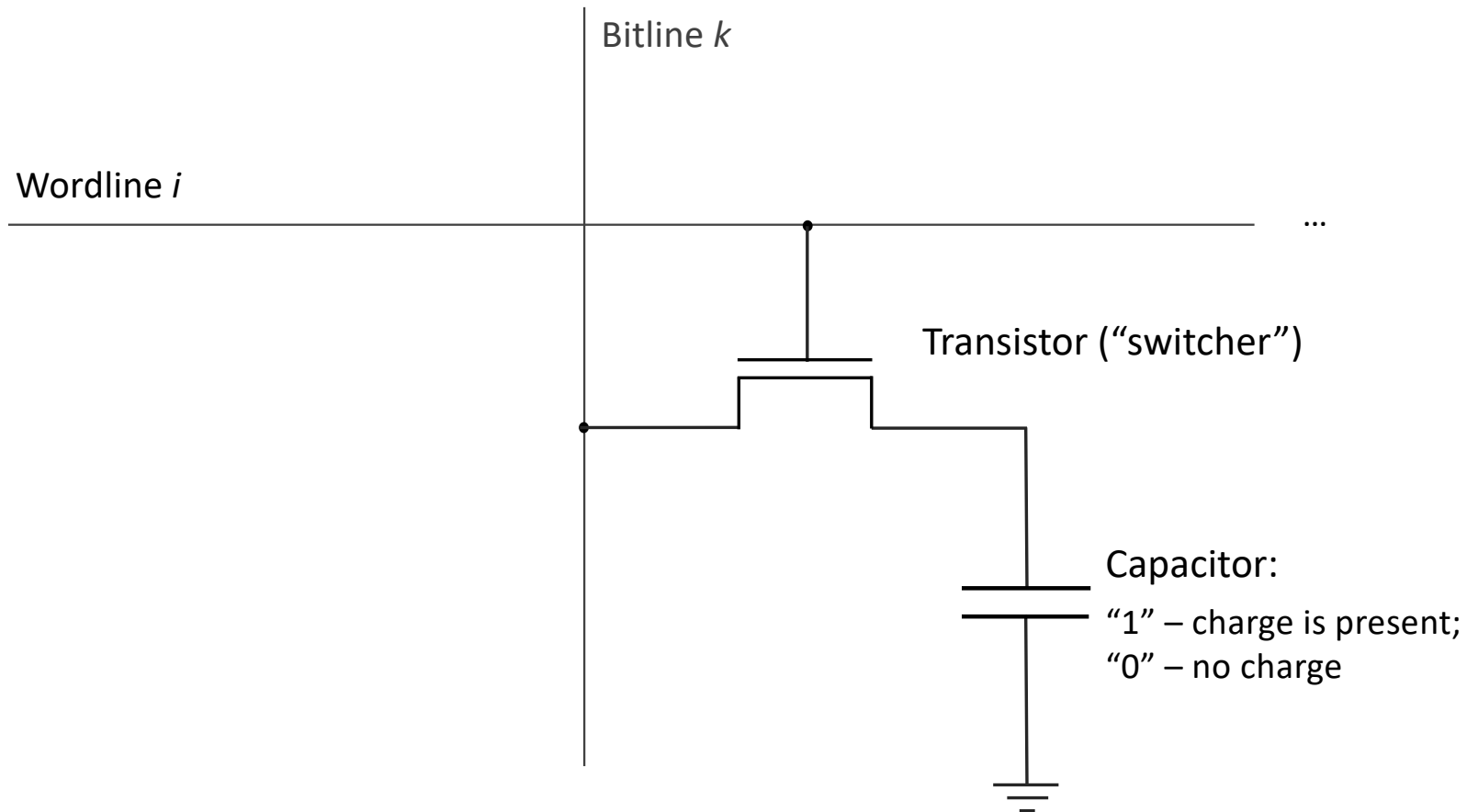
A More Compact Graphical Notation for Electrical Circuits



A More Compact Graphical Notation for Electrical Circuits

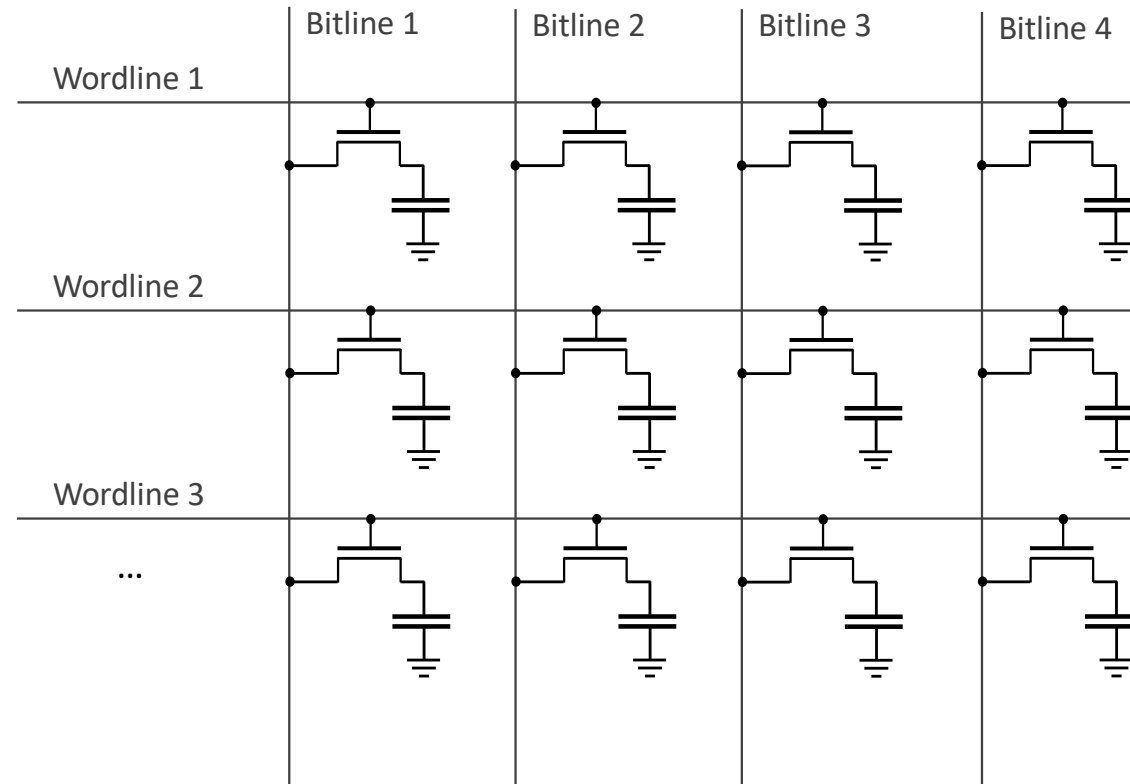


A More Compact Graphical Notation for Electrical Circuits



DRAM memory – a set of memory cells
(each cell contains 1 bit of data)

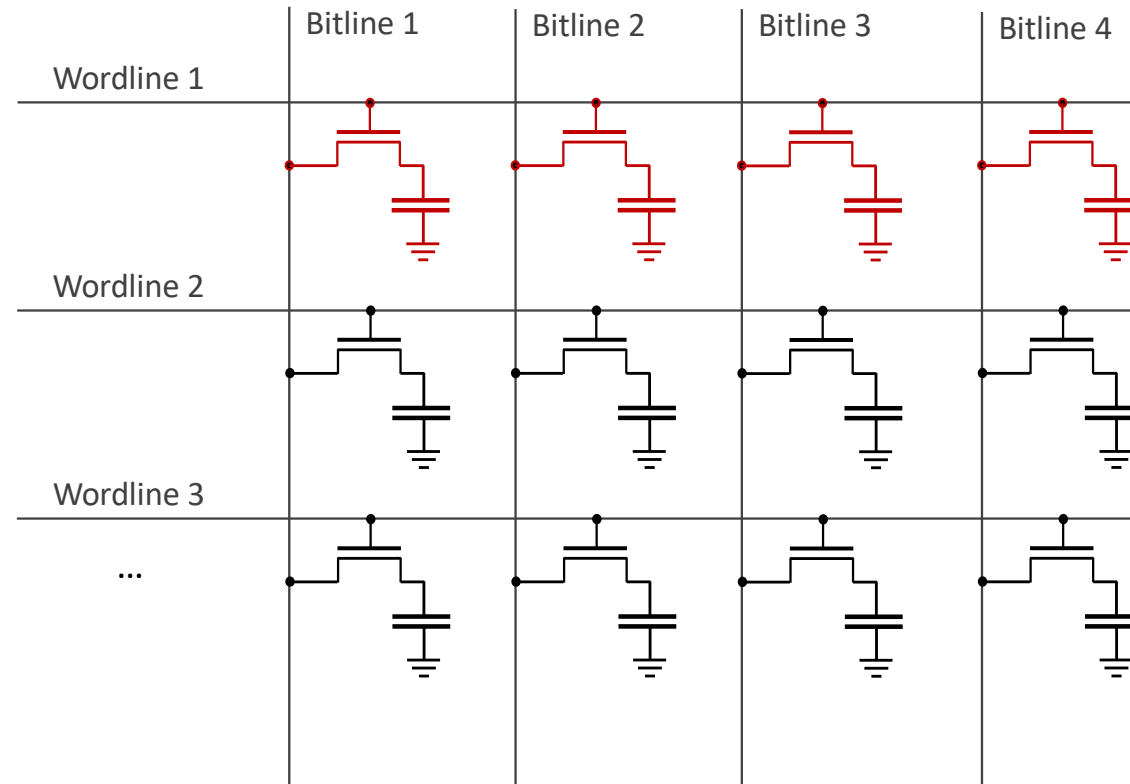
DRAM Memory: the Work Principle



DRAM memory – a set of memory cells
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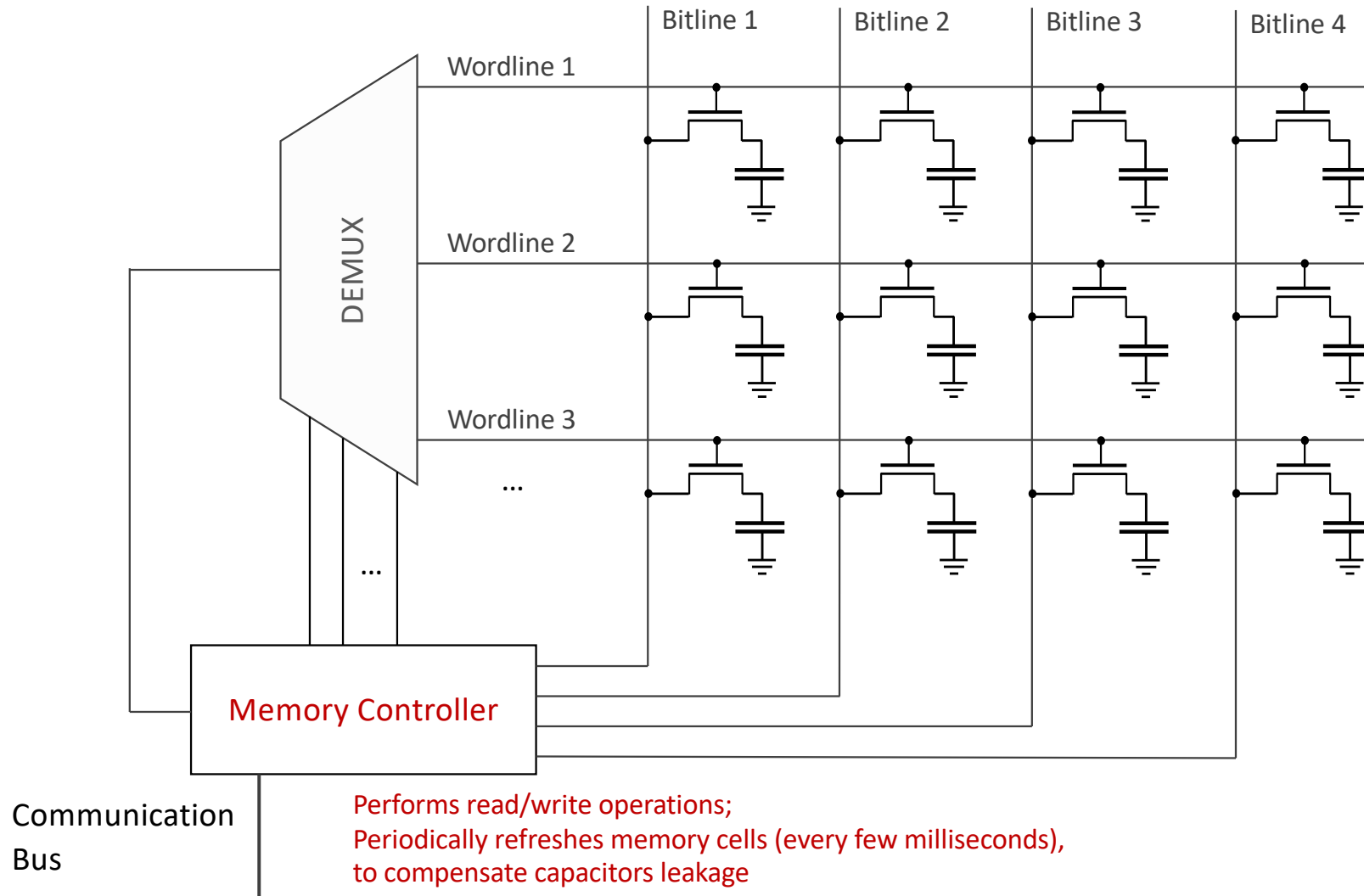
DRAM Memory: the Work Principle

Several memory cells are
connected to the same wordline

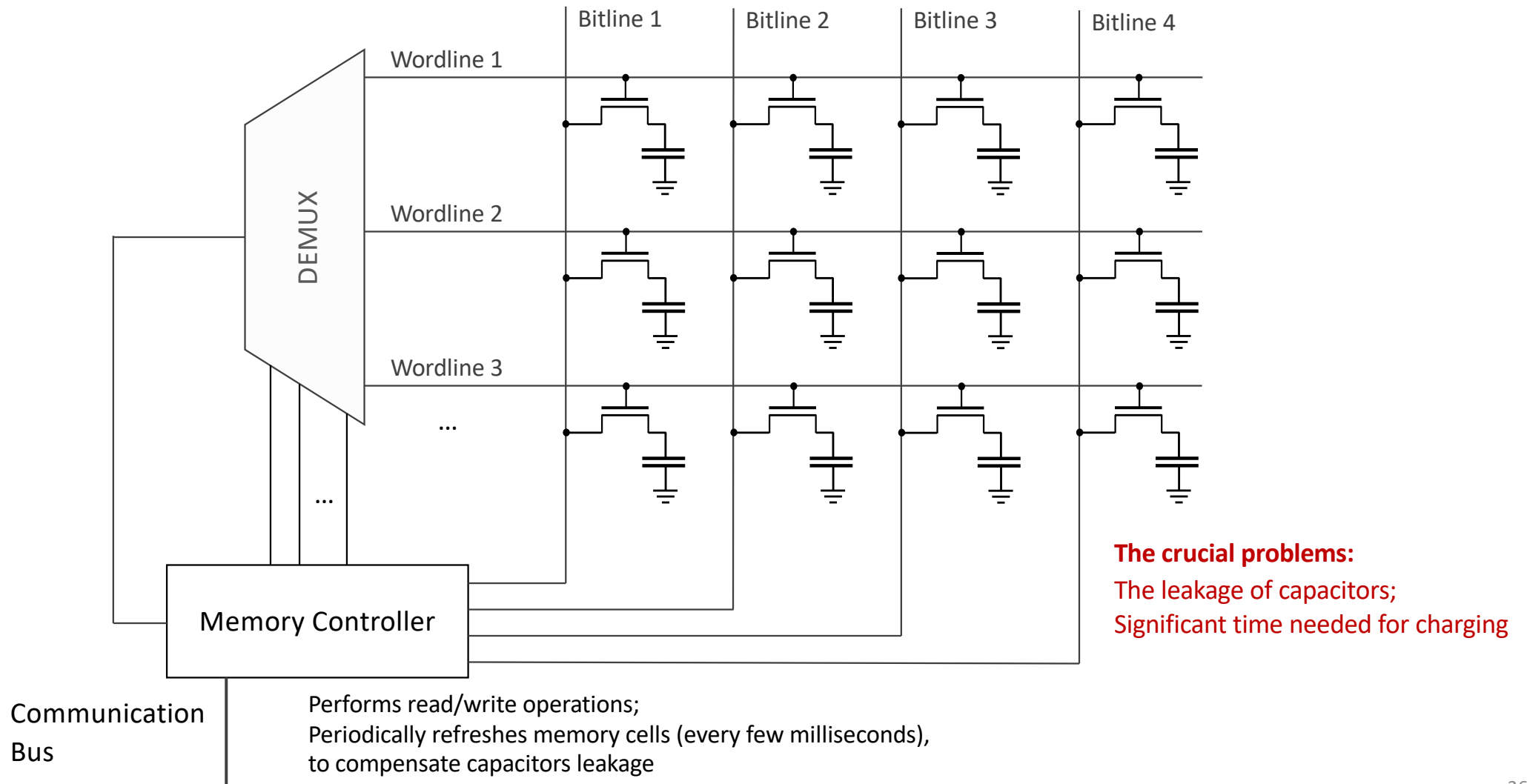


Memory controller operates with memory cells,
by using demultiplexors, encoders, etc.

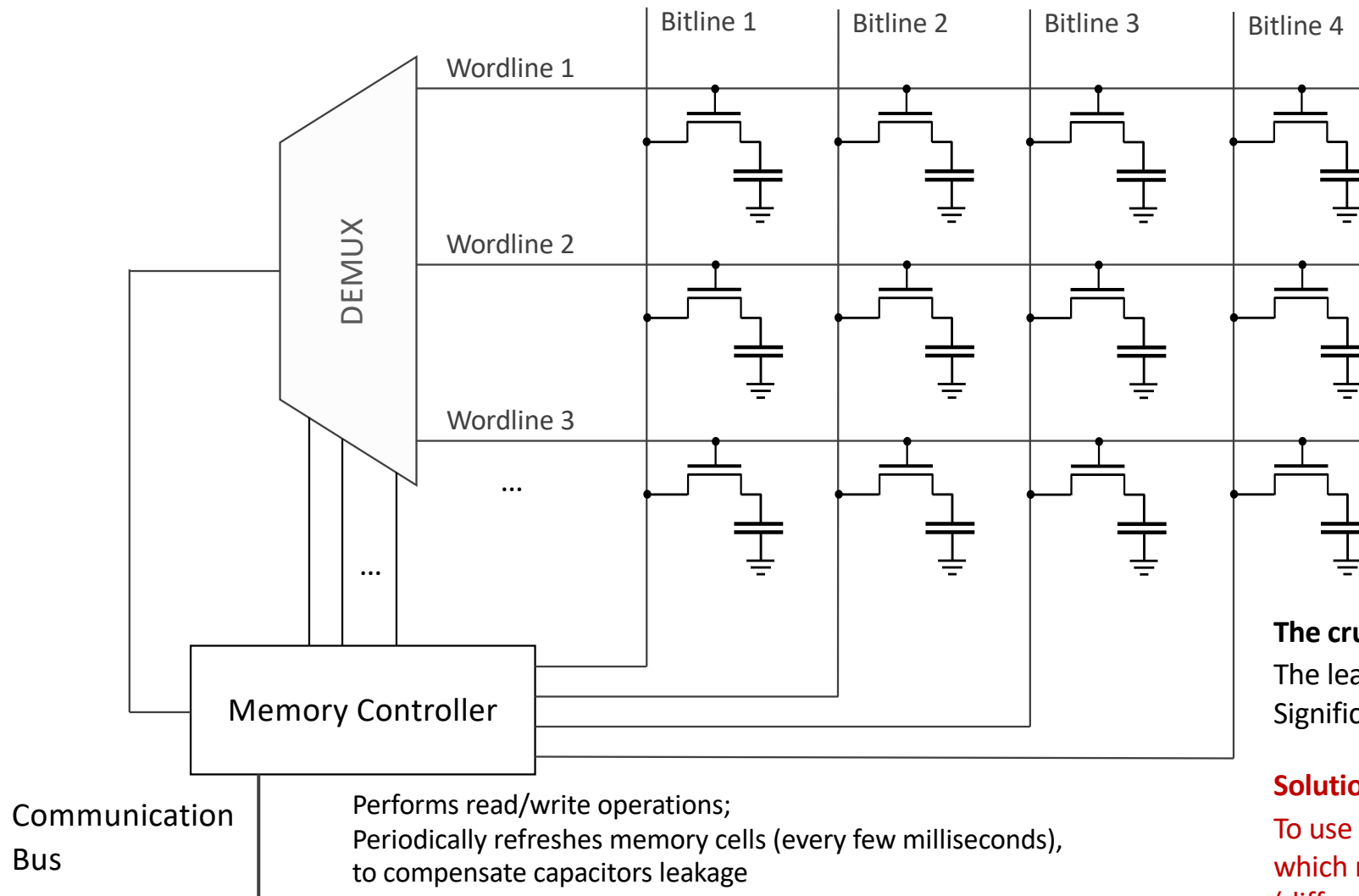
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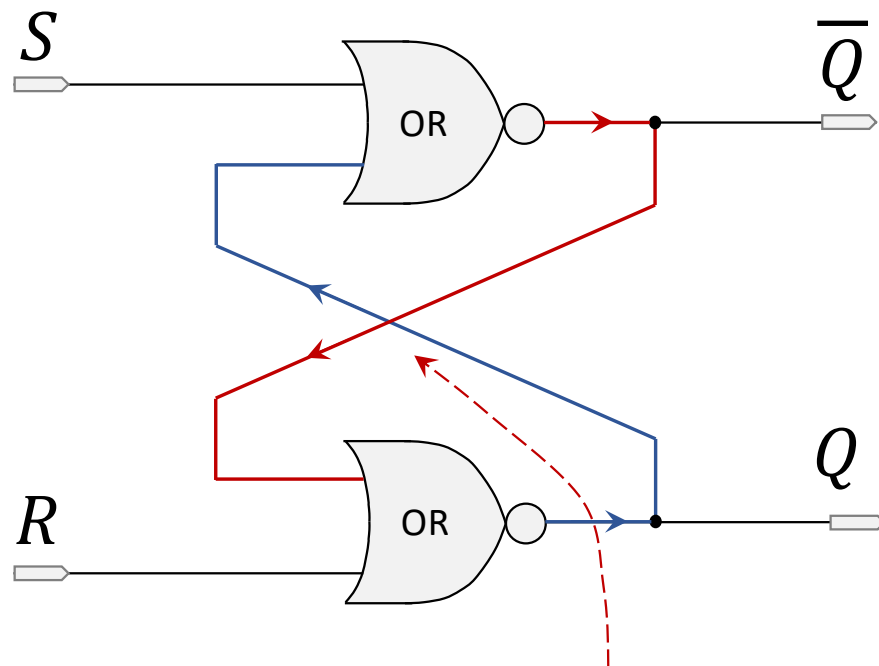
The crucial problems:

The leakage of capacitors;
Significant time needed for charging

Solution:

To use SRAM,
which relies on latches and flip-flops
(different from capacitors)

Latch: an electronic circuit to store one bit of information

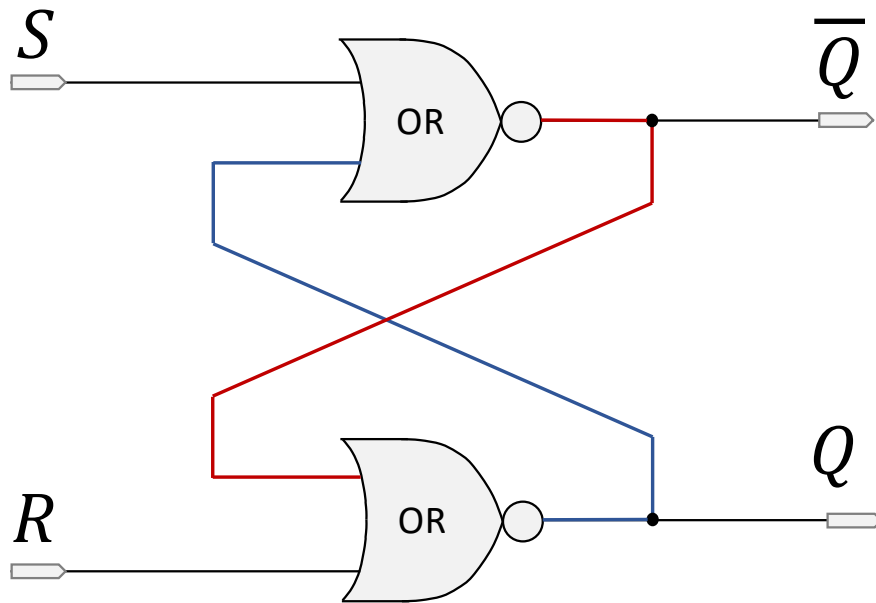


S	R	Q
1	0	1
0	1	0
0	0	Q^{prev}
1	1	Illegal inputs

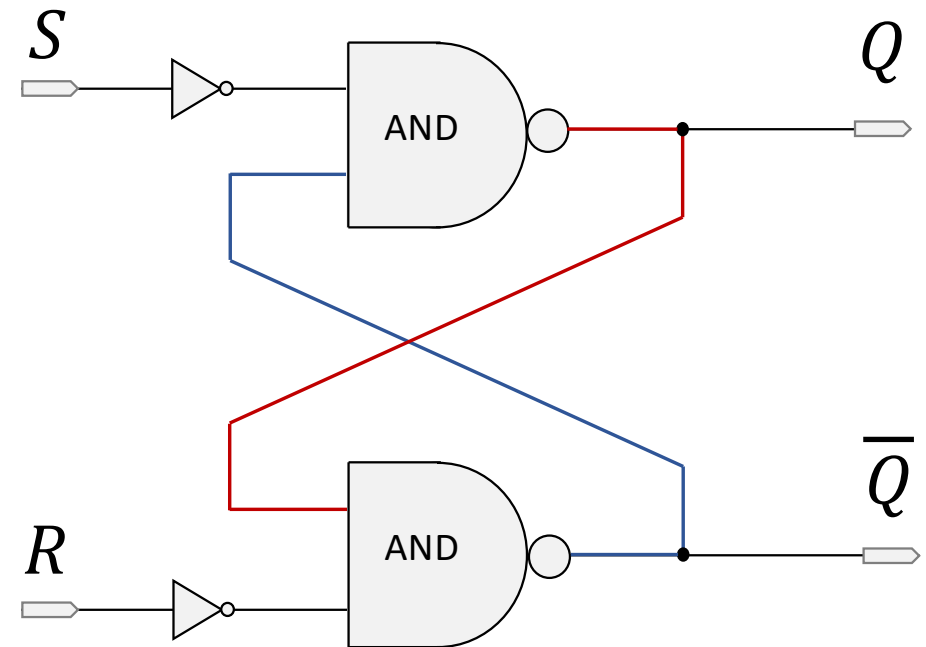
Cross-coupled connection of logic gates – the key feature of latches and flip-flops: the output signal of one gate serves as an input for another gate

Latch: multiple logic implementations are available

1) Implementation by using NOR logic gates:

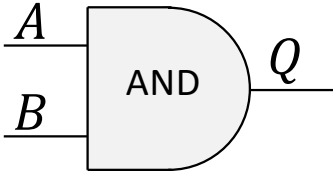
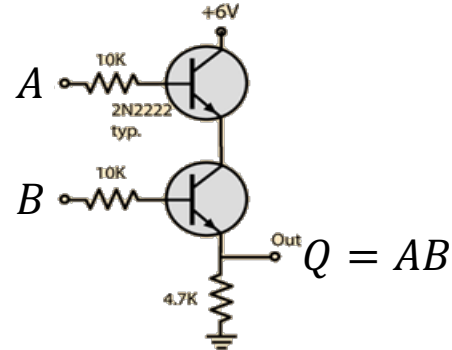
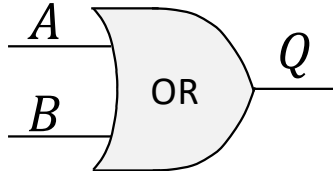
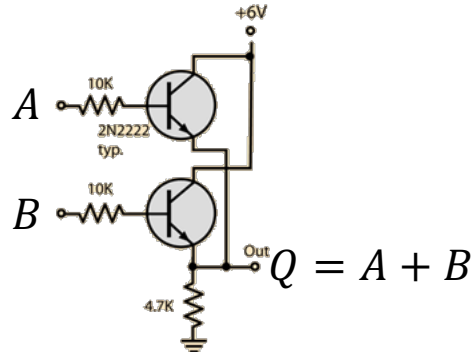
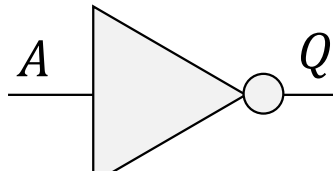
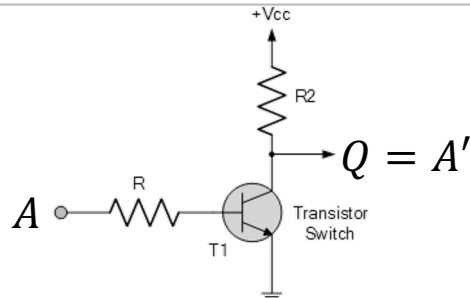


2) by using NAND logic gates:



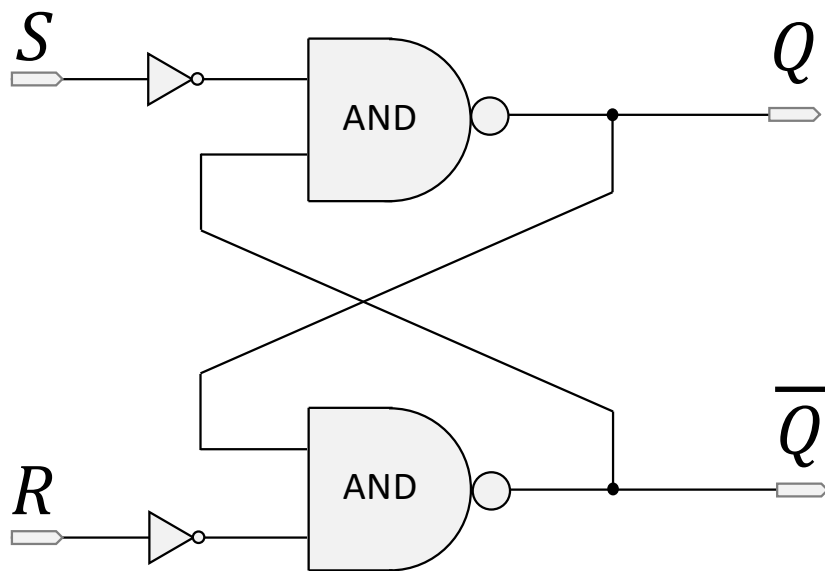
These representations are logical oversimplified representations, hiding many implementation details

Recap: Each logic gate is an electronic circuit, implemented by using transistors

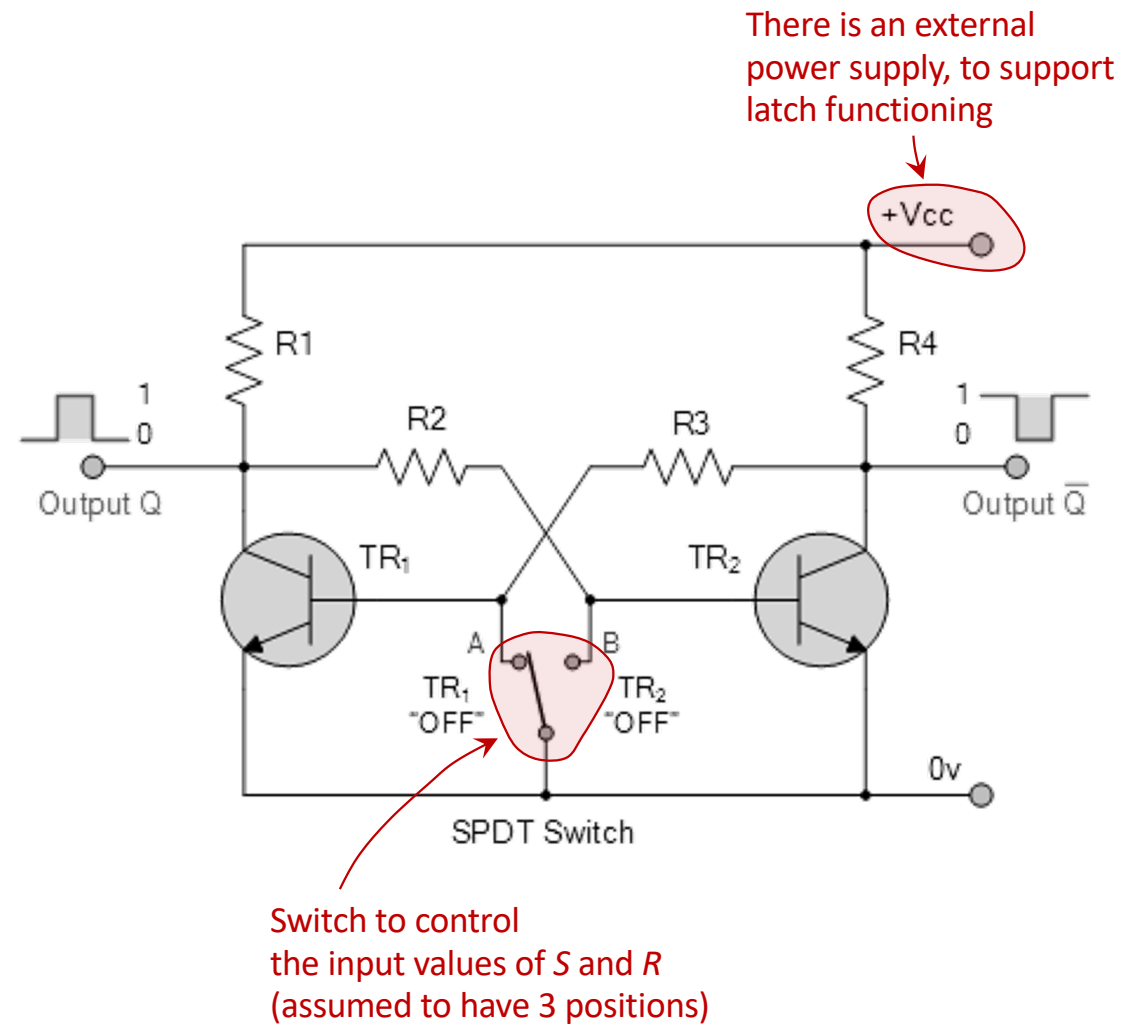
Logic Gate	Symbolic Representation	Truth Table	Implementation with Transistors															
AND		<table><tr><th>A</th><th>B</th><th>Q=AB</th></tr><tr><td>0</td><td>0</td><td>0</td></tr><tr><td>1</td><td>0</td><td>0</td></tr><tr><td>0</td><td>1</td><td>0</td></tr><tr><td>1</td><td>1</td><td>1</td></tr></table>	A	B	Q=AB	0	0	0	1	0	0	0	1	0	1	1	1	
A	B	Q=AB																
0	0	0																
1	0	0																
0	1	0																
1	1	1																
OR		<table><tr><th>A</th><th>B</th><th>Q=A+B</th></tr><tr><td>0</td><td>0</td><td>0</td></tr><tr><td>1</td><td>0</td><td>1</td></tr><tr><td>0</td><td>1</td><td>1</td></tr><tr><td>1</td><td>1</td><td>1</td></tr></table>	A	B	Q=A+B	0	0	0	1	0	1	0	1	1	1	1	1	
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NOT		<table><tr><th>A</th><th>Q=A'</th></tr><tr><td>0</td><td>1</td></tr><tr><td>1</td><td>0</td></tr></table>	A	Q=A'	0	1	1	0										
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Transistor implementations are taken from <http://hyperphysics.phy-astr.gsu.edu/hbase/Electronic/trangate.html#c1> and https://www.electronics-tutorials.ws/logic/logic_4.html

Latch Logical representation:

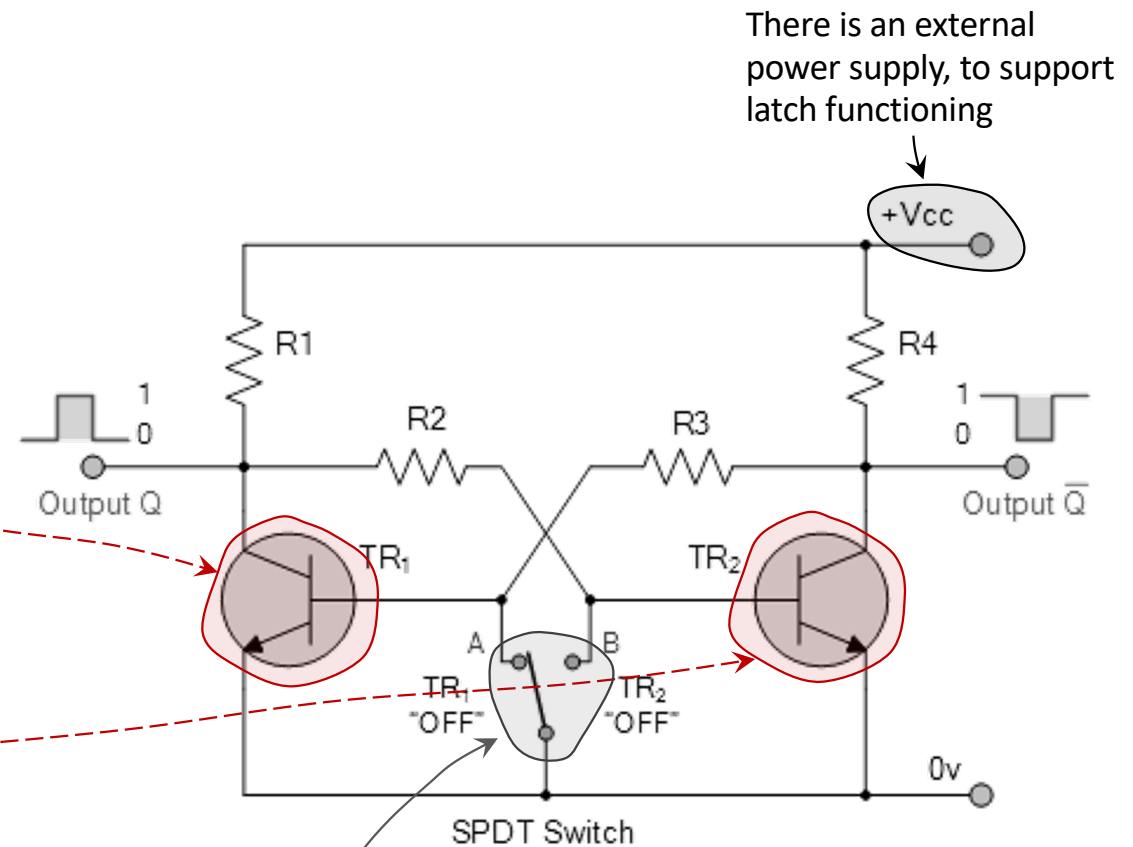
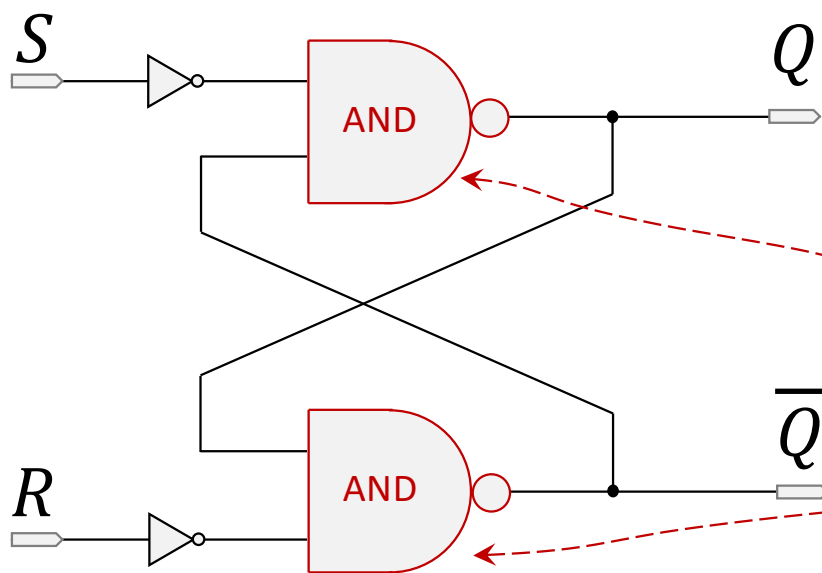


Electrical circuit implementation (one of many):



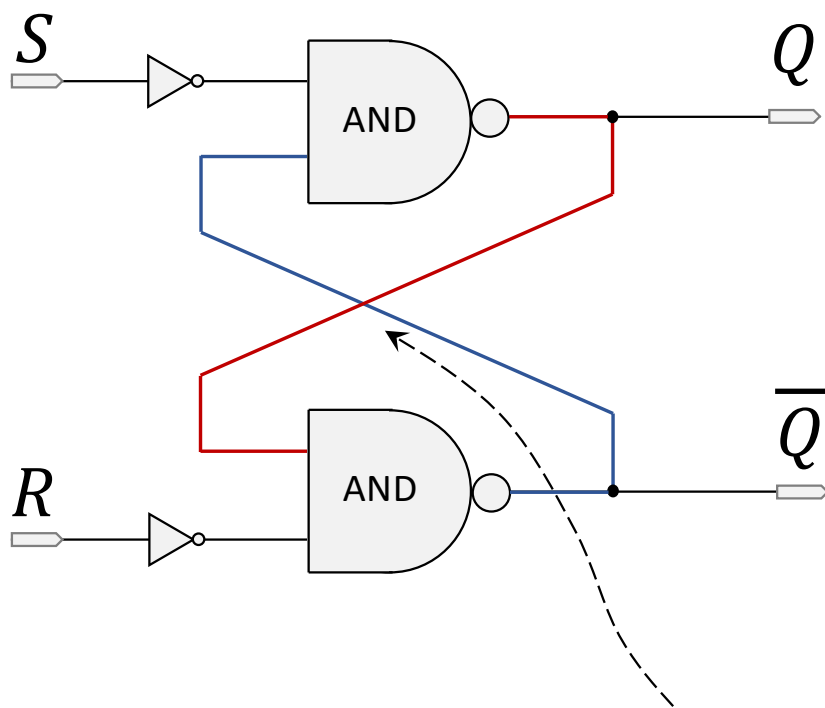
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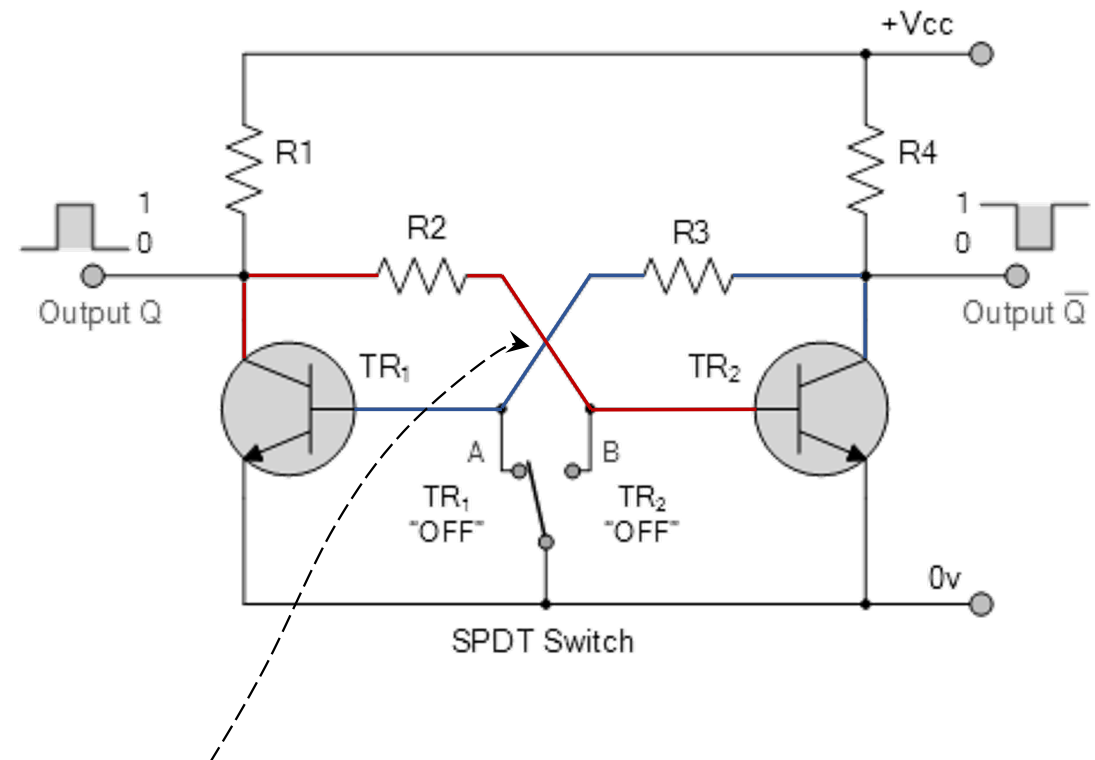


Switch to control
the input values of S and R
(assumed to have 3 positions)

Latch Logical representation:

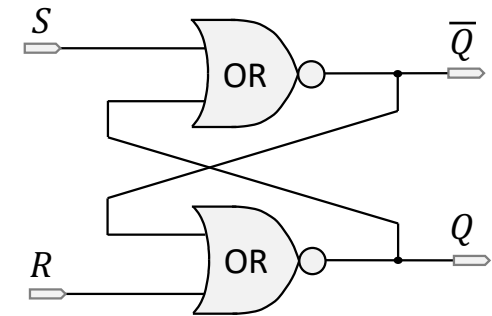
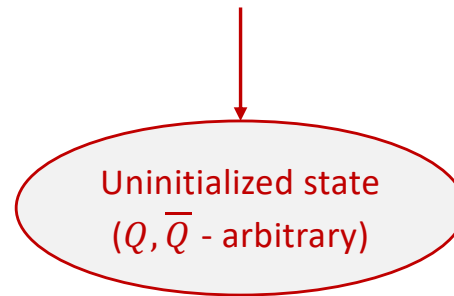


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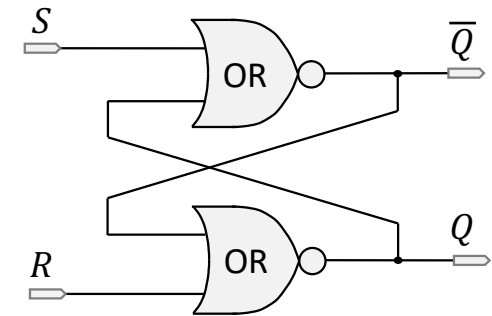
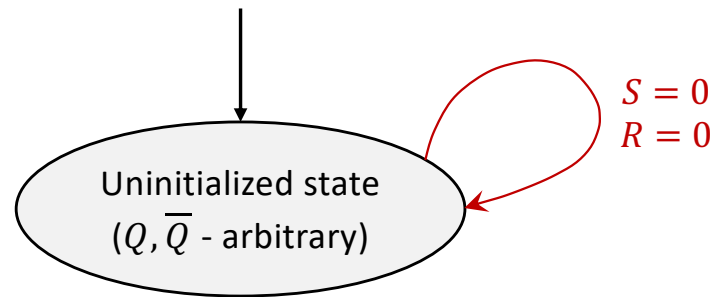


Cross-coupled connections between gates and corresponding transistors

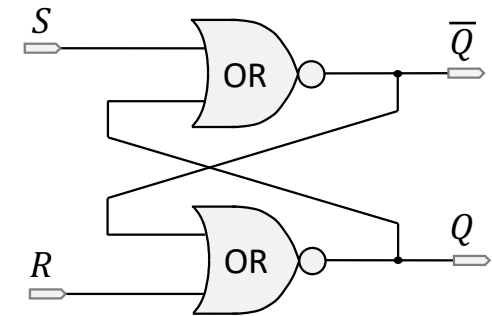
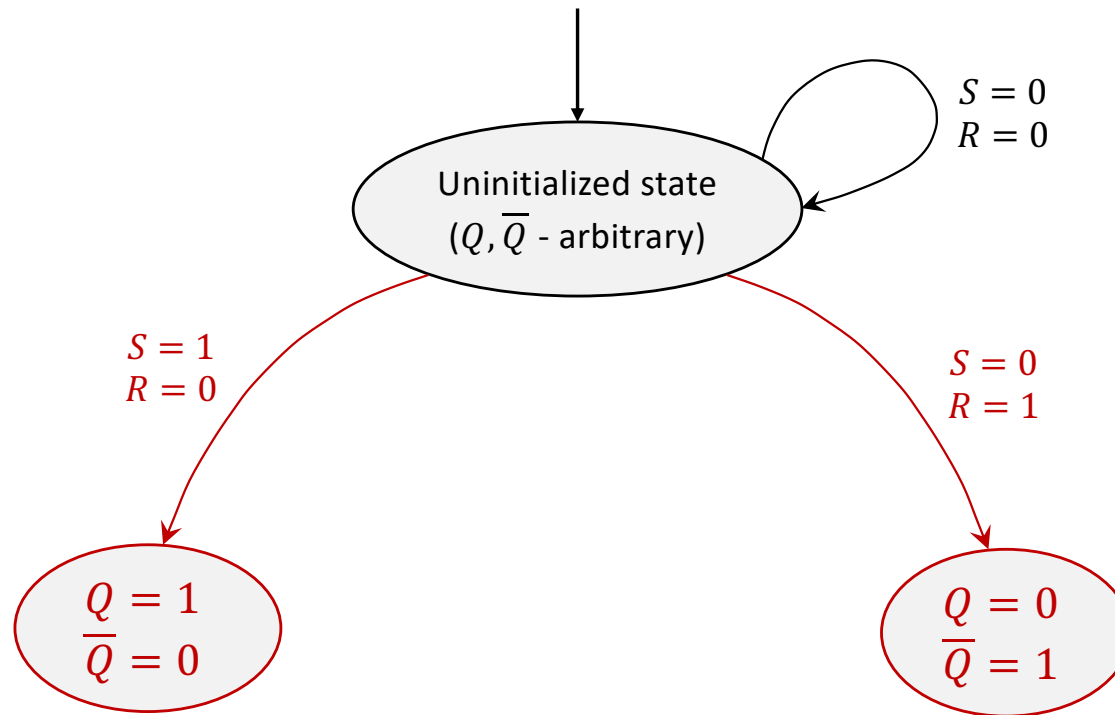
State-Transition Diagram for a Latch



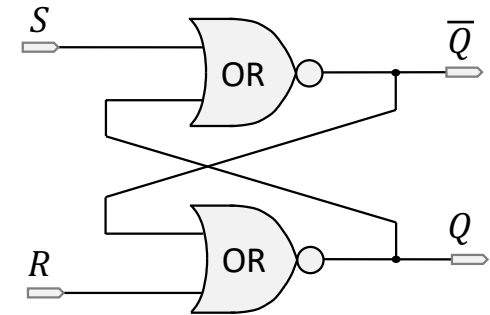
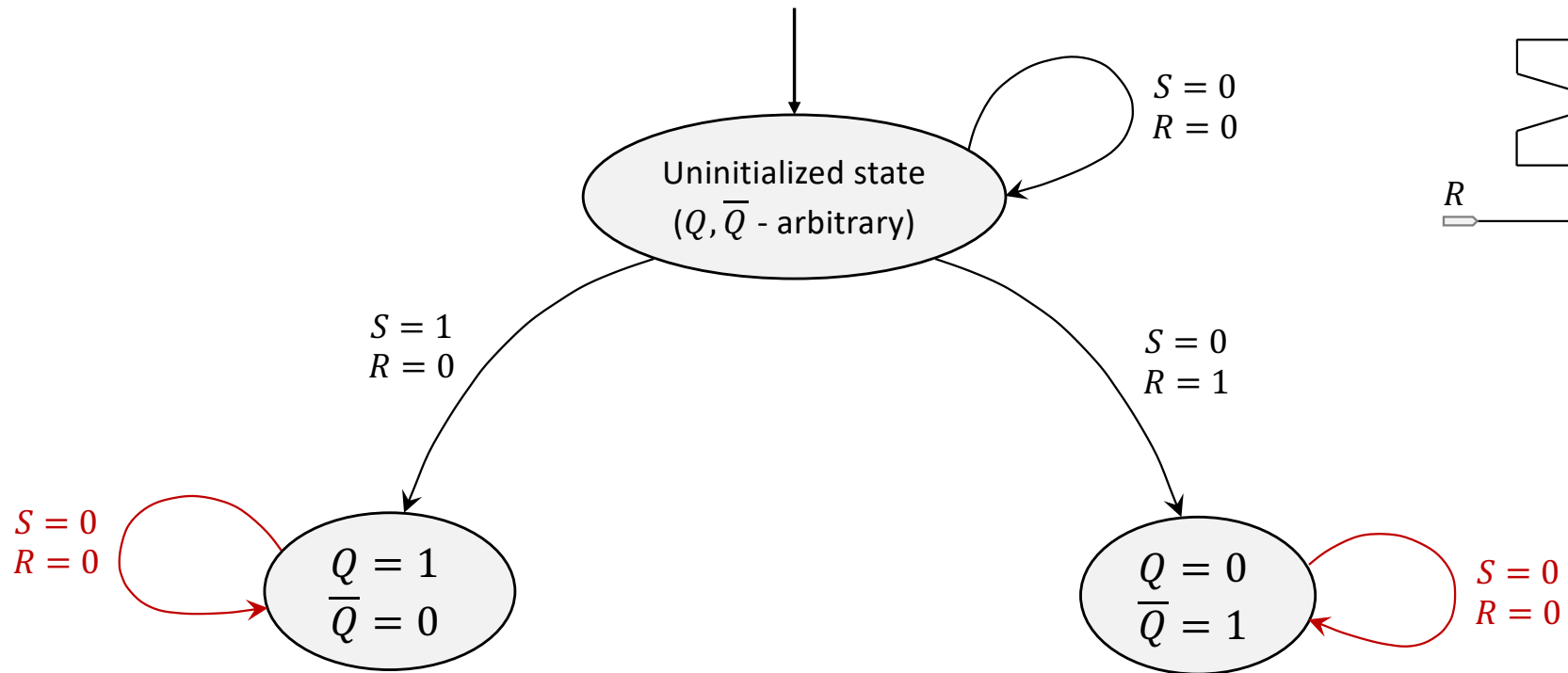
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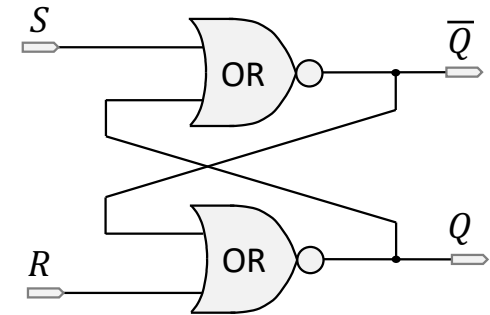
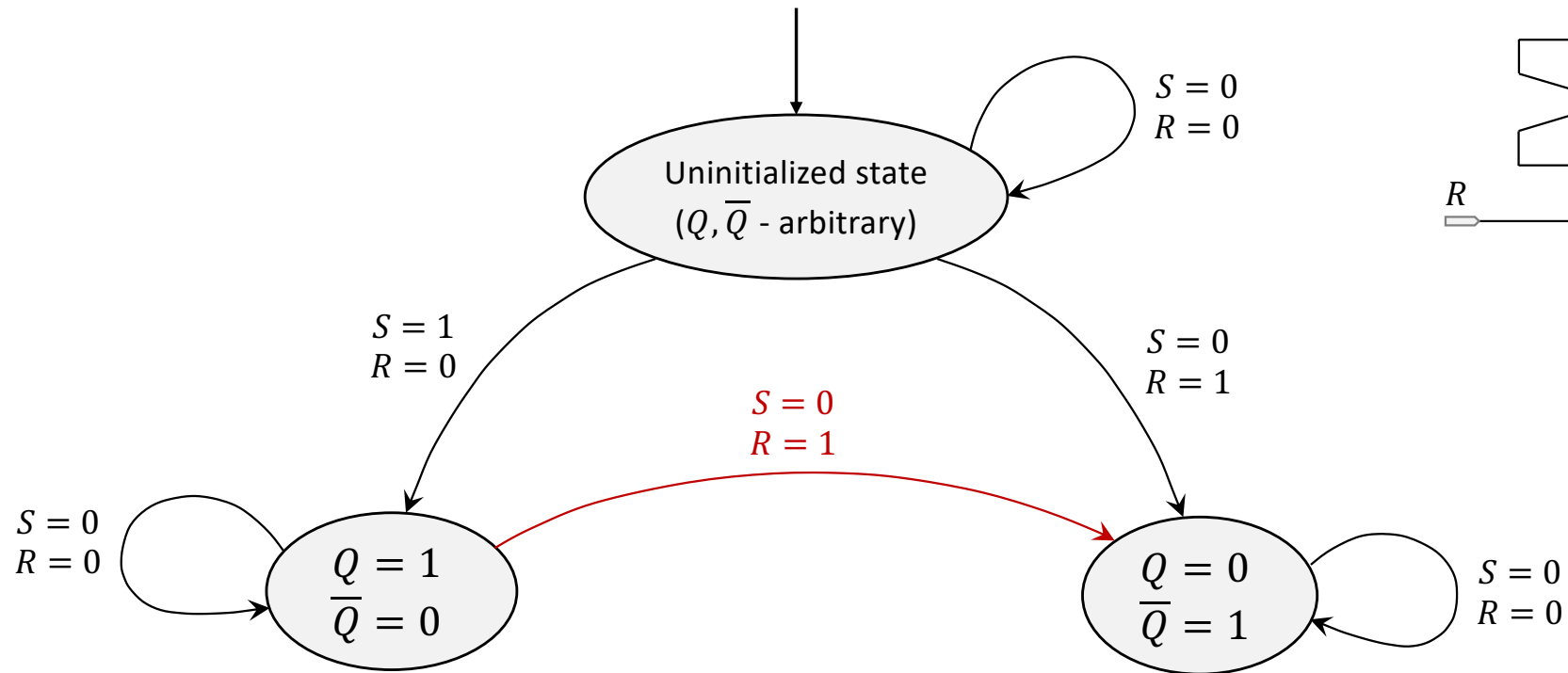
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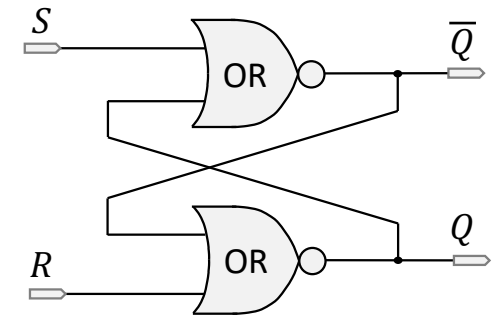
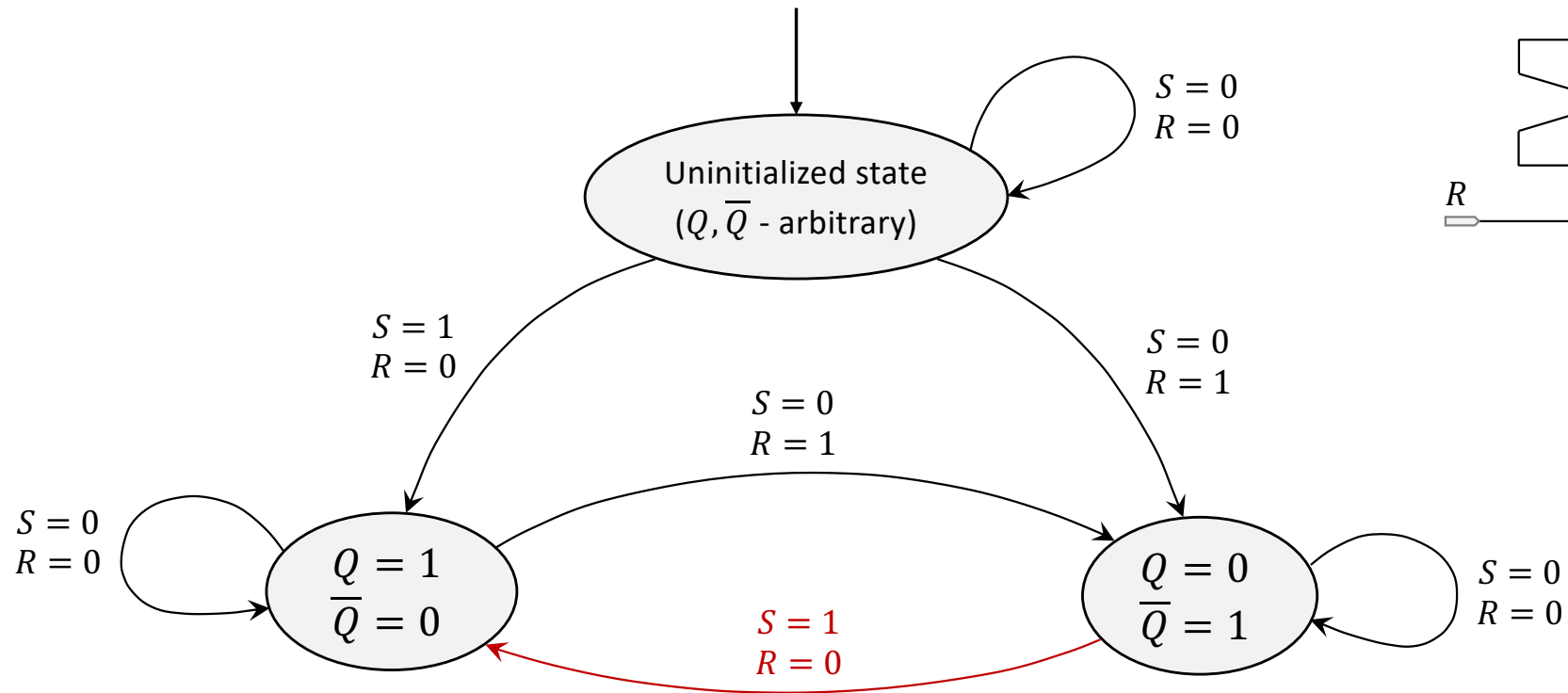
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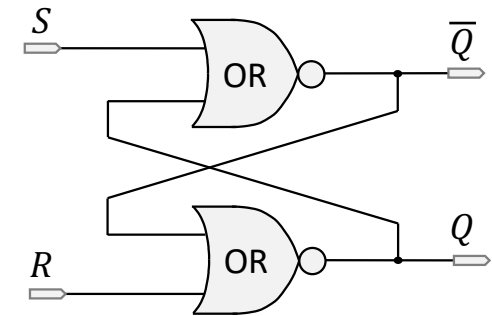
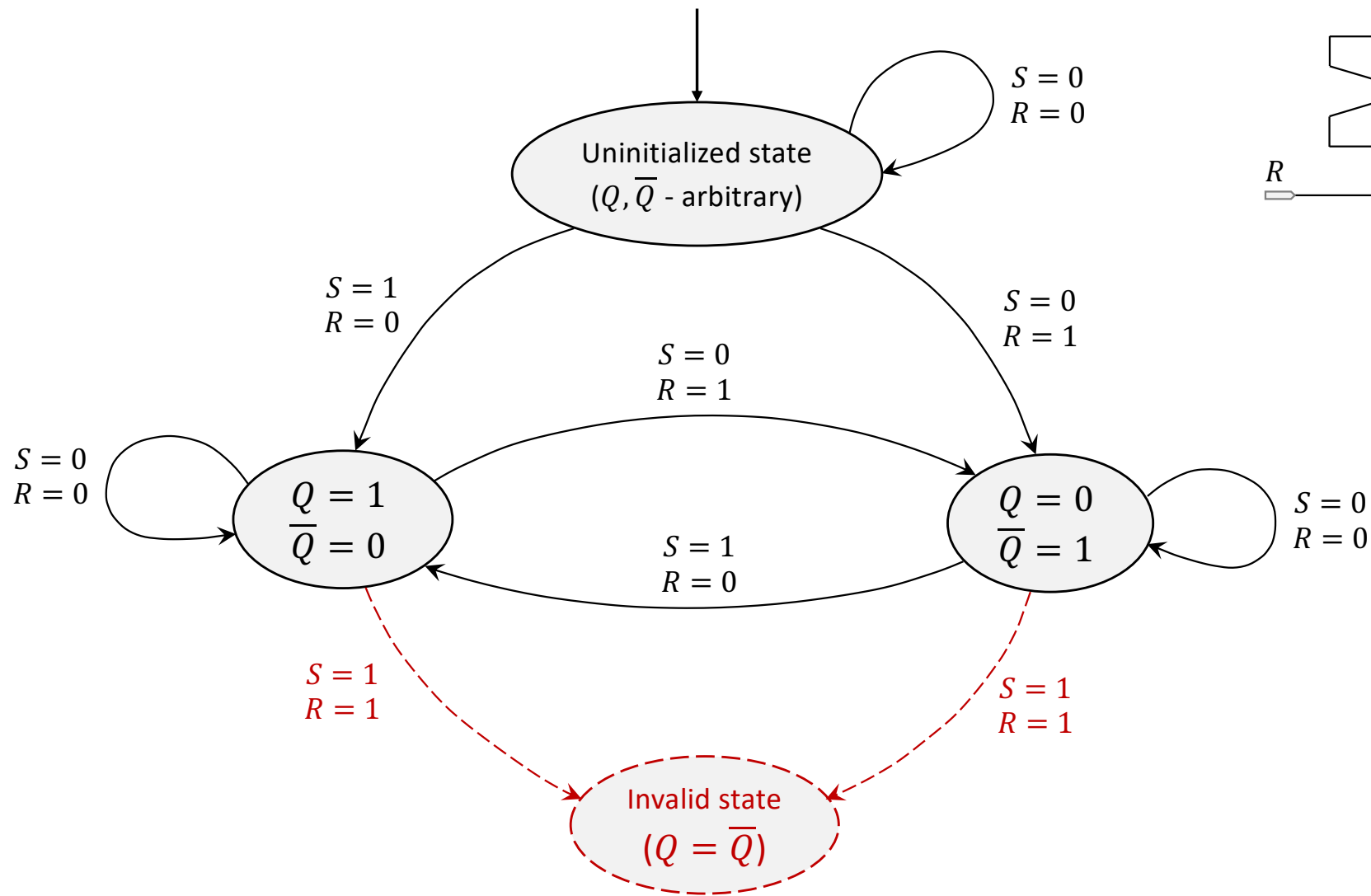
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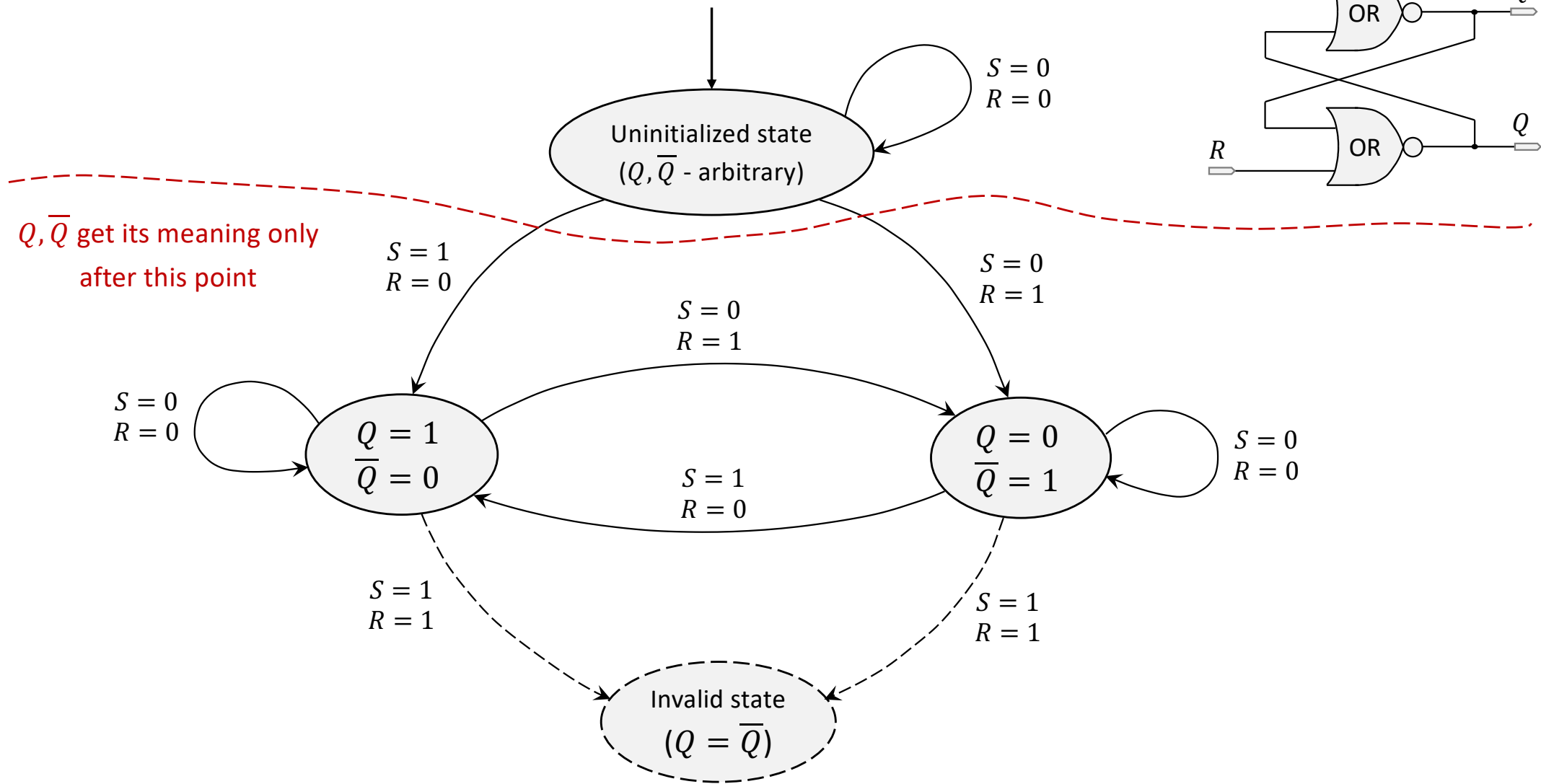
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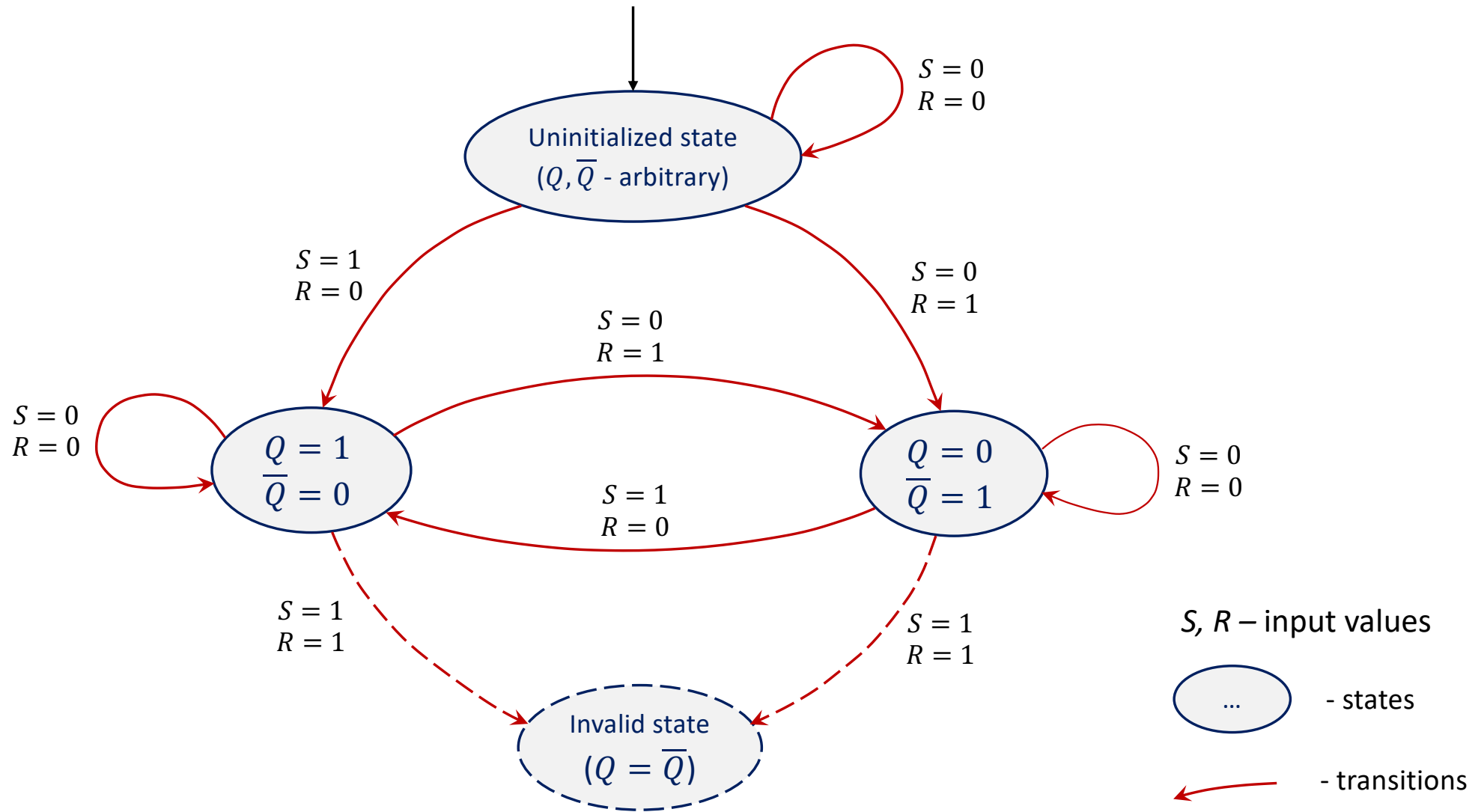
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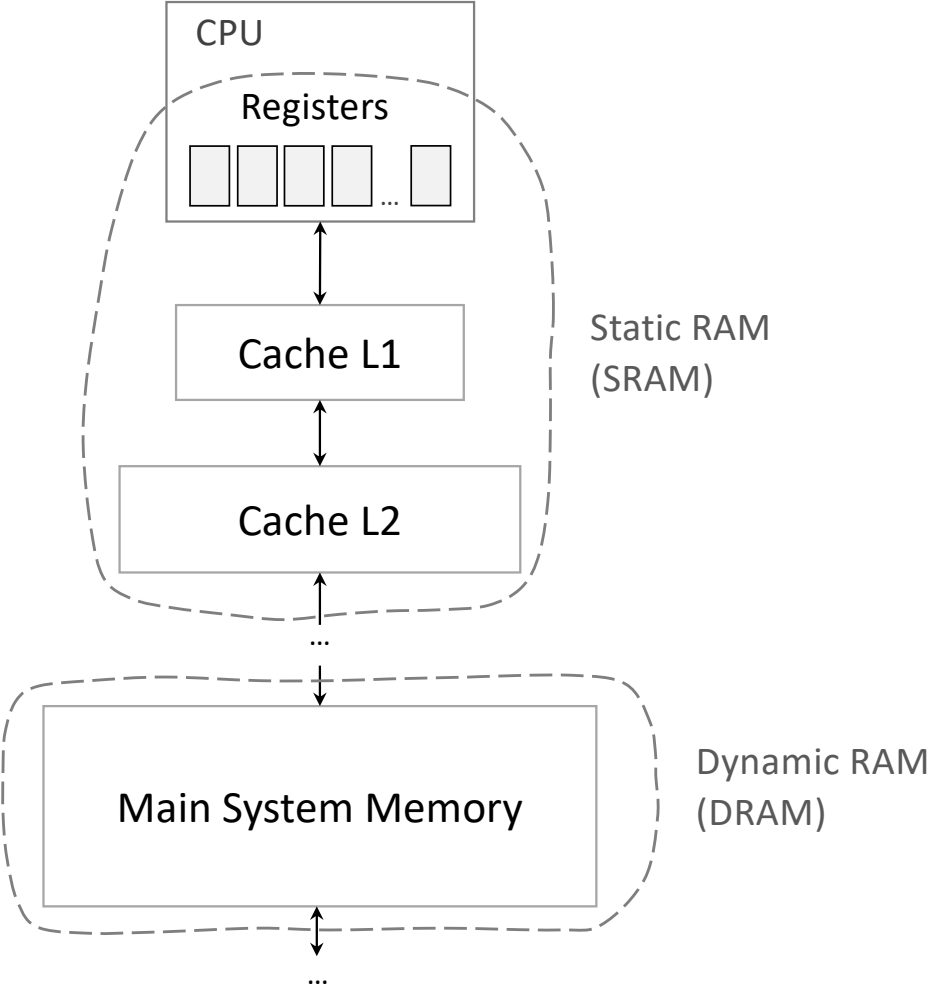
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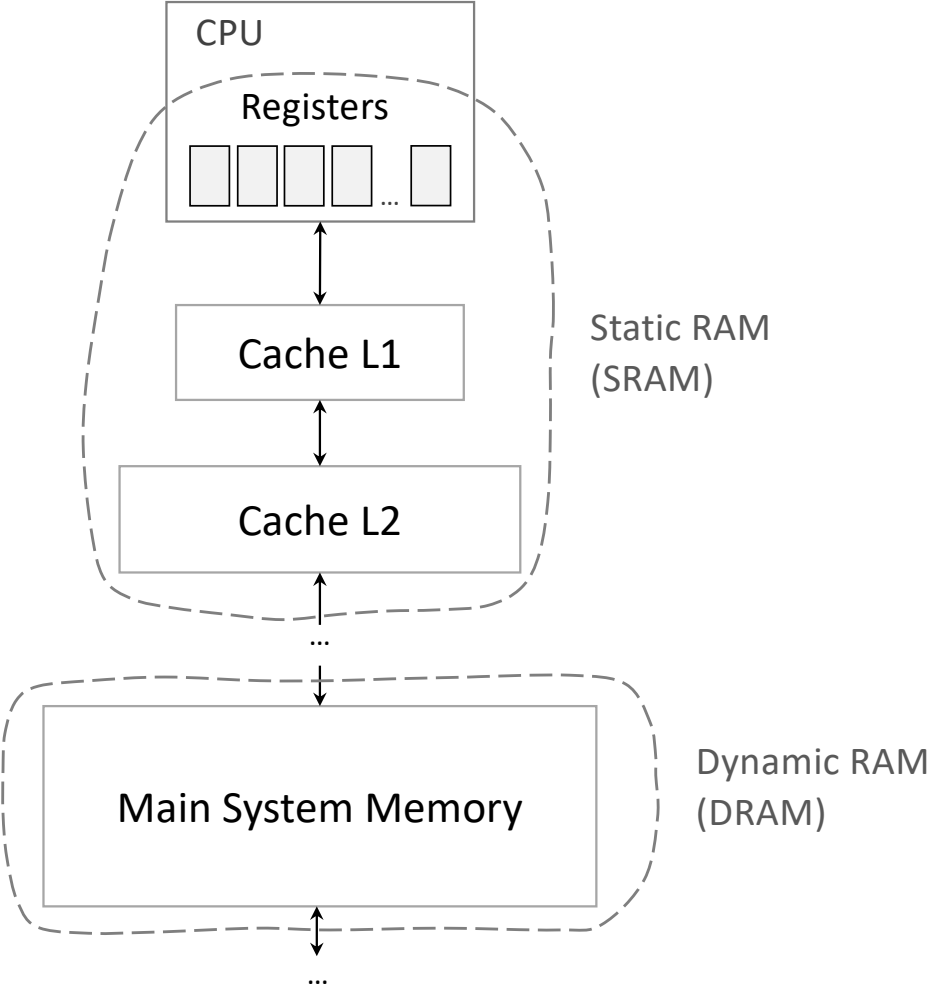


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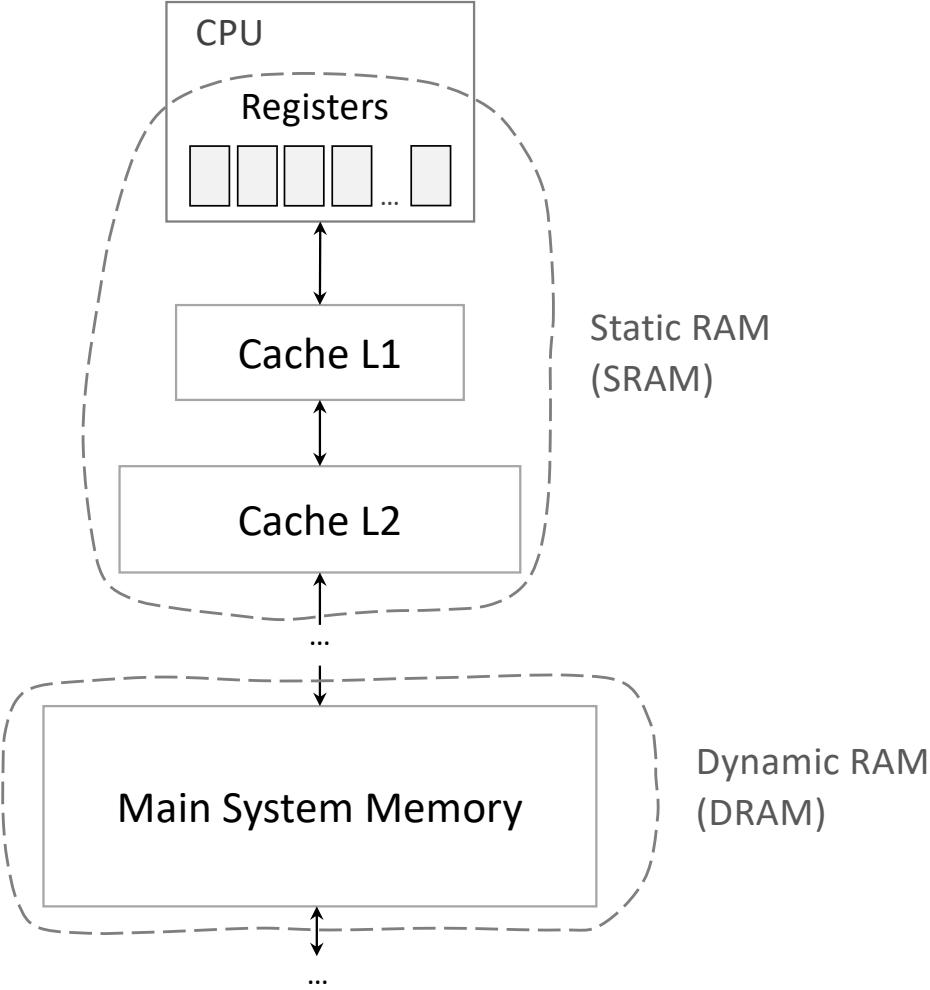
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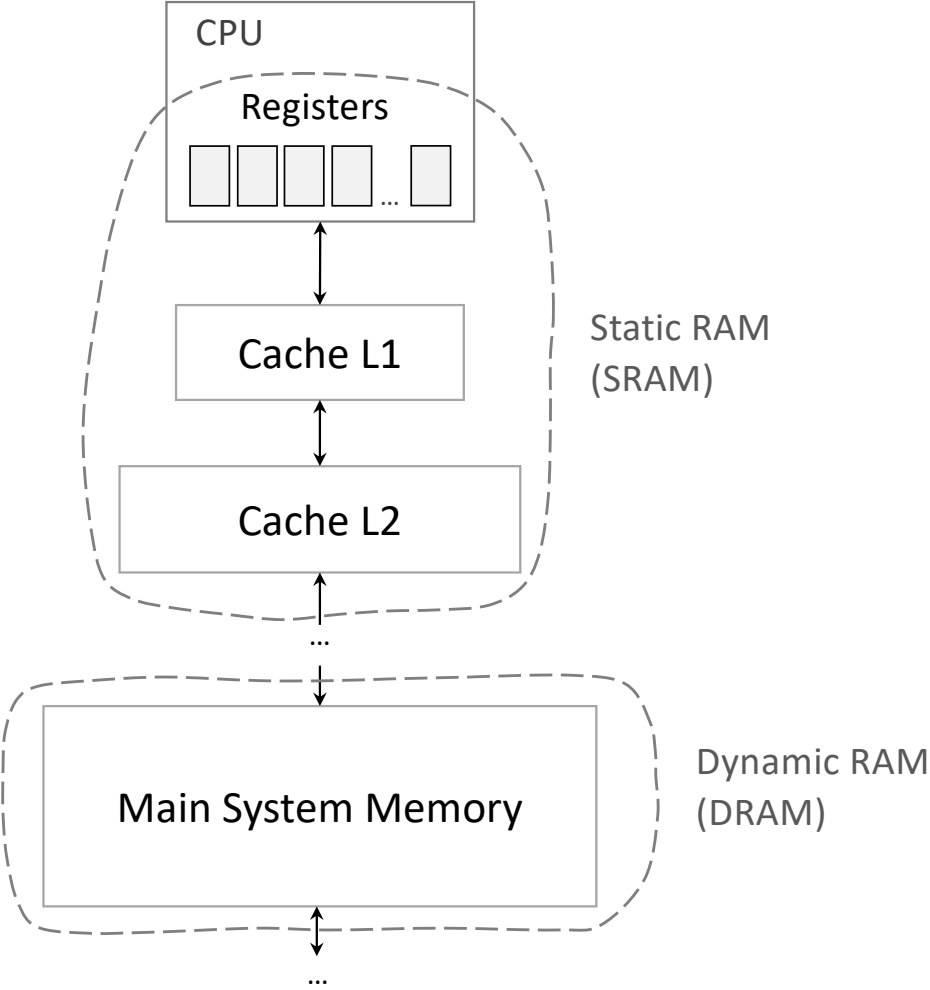
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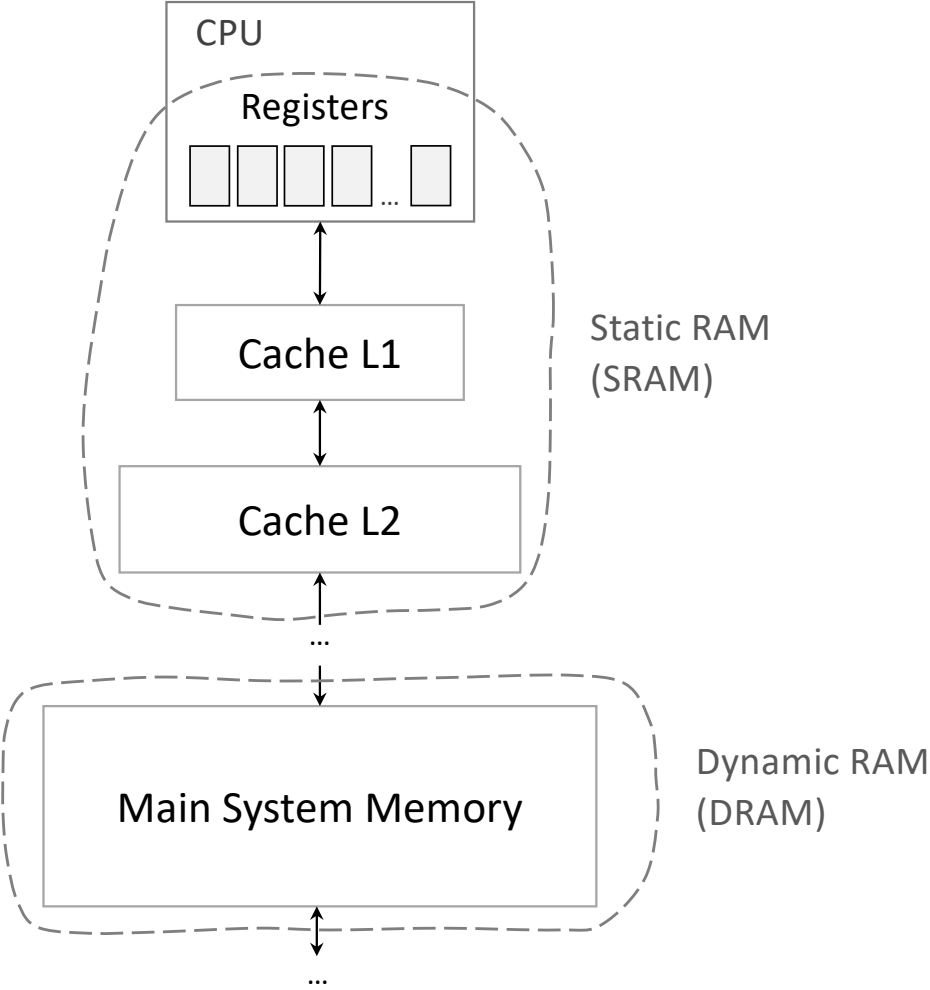
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Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



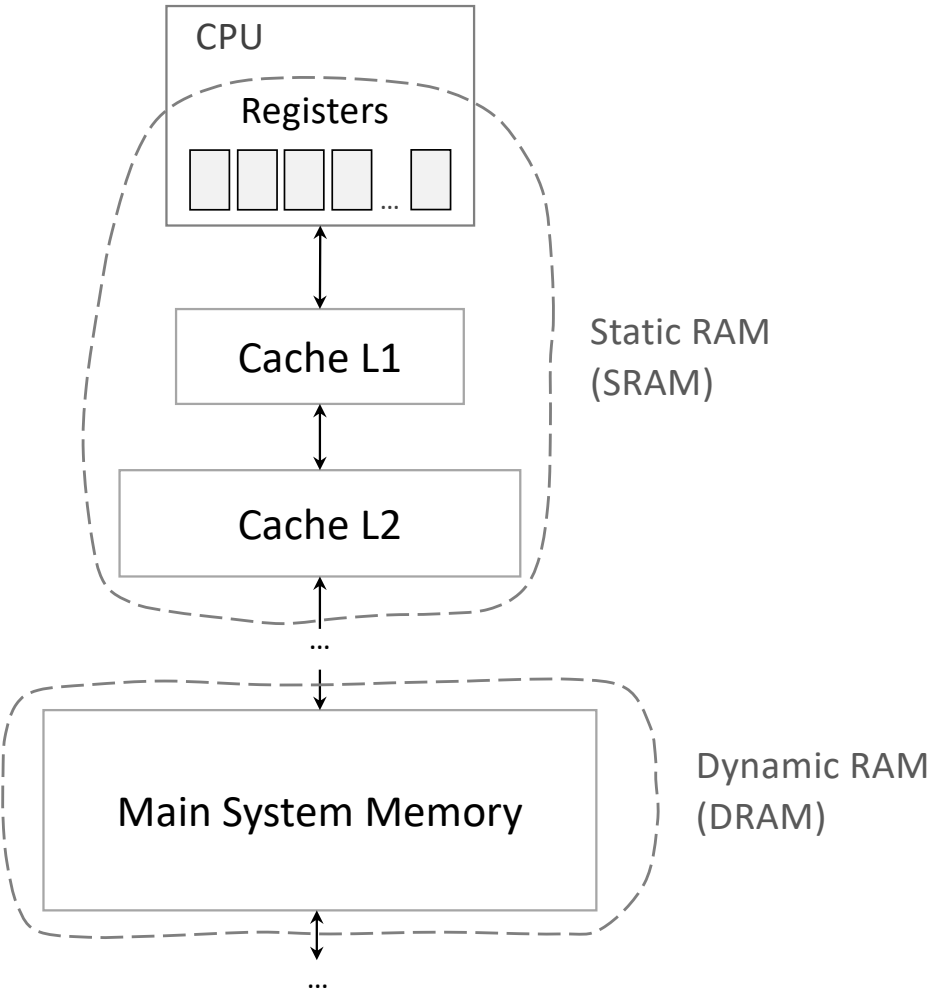
Characteristic	SRAM	DRAM
Access Speed	Faster	Slower
Storage Capacity	Smaller	Larger
Storage Element	Flip-flop	Capacitor
Usage		
Cost		
Power Consumption		
Organisation		
Power Leakage		
Chip Reliability		
Volatility		
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



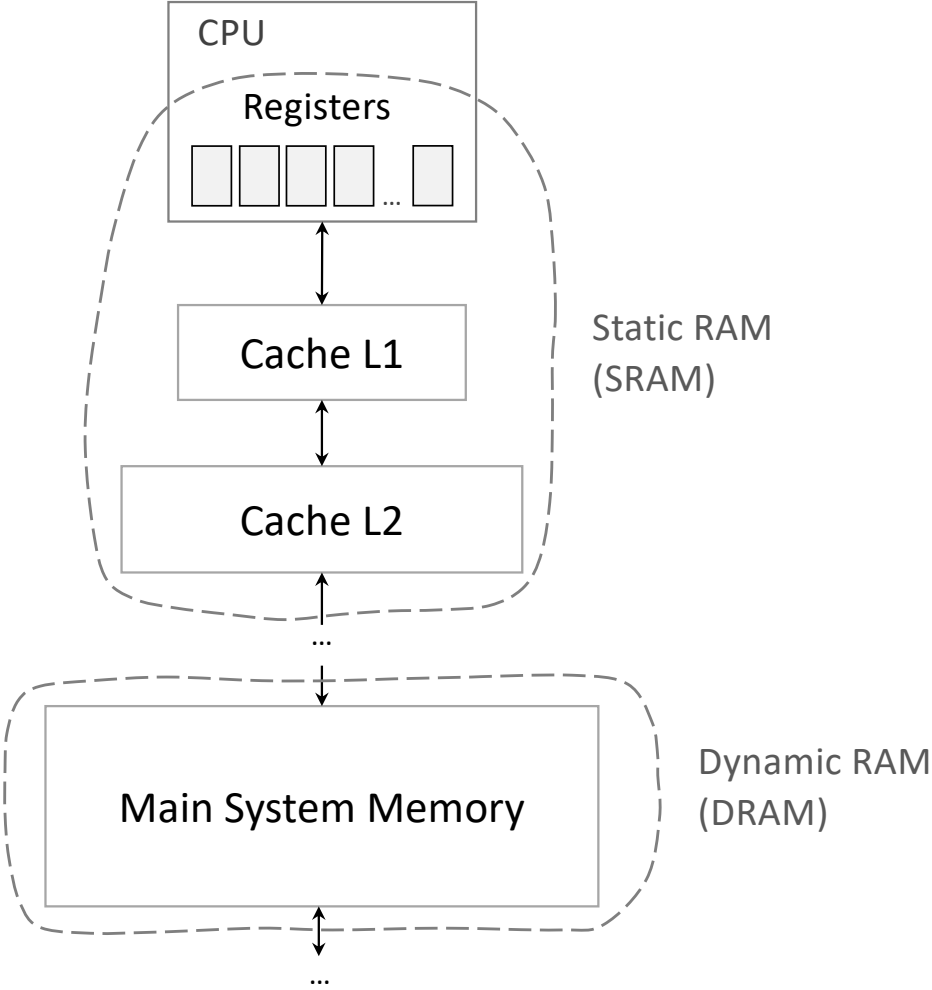
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The Comparison of DRAM and SRAM Memory Types



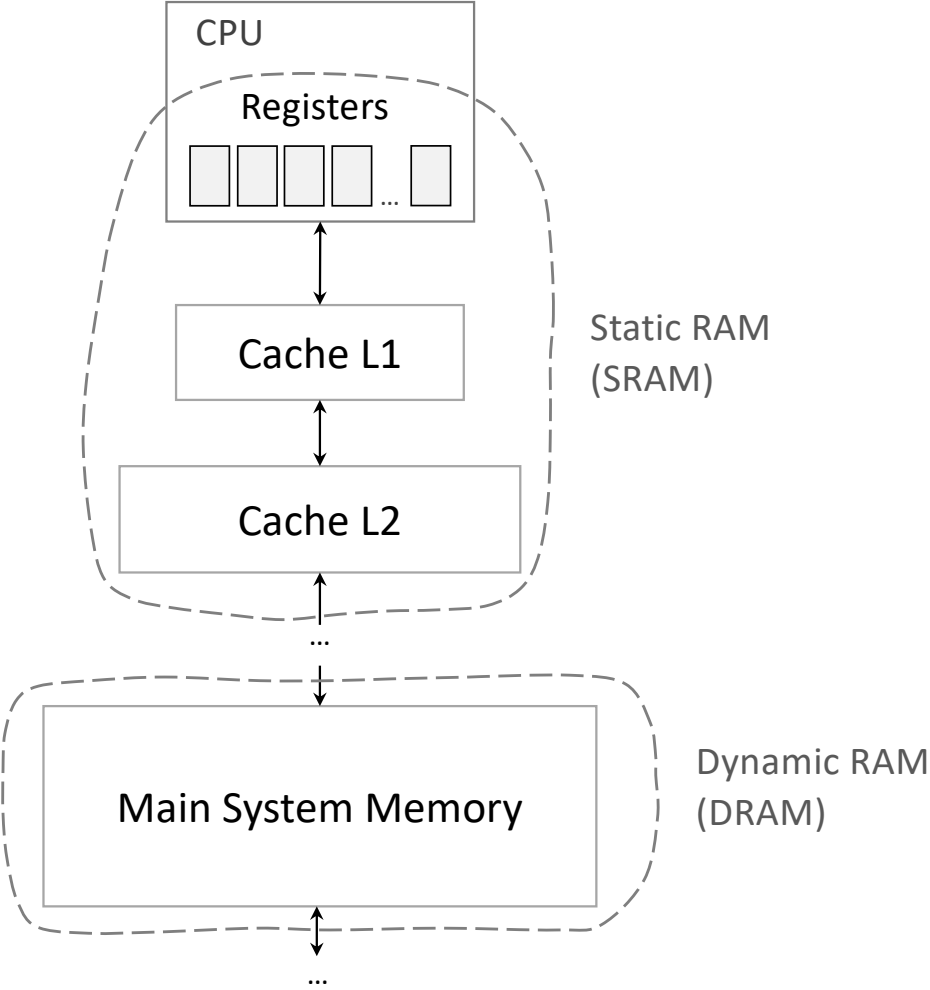
Characteristic	SRAM	DRAM
Access Speed	Faster	Slower
Storage Capacity	Smaller	Larger
Storage Element	Flip-flop	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption		
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Chip Reliability		
Volatility		
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



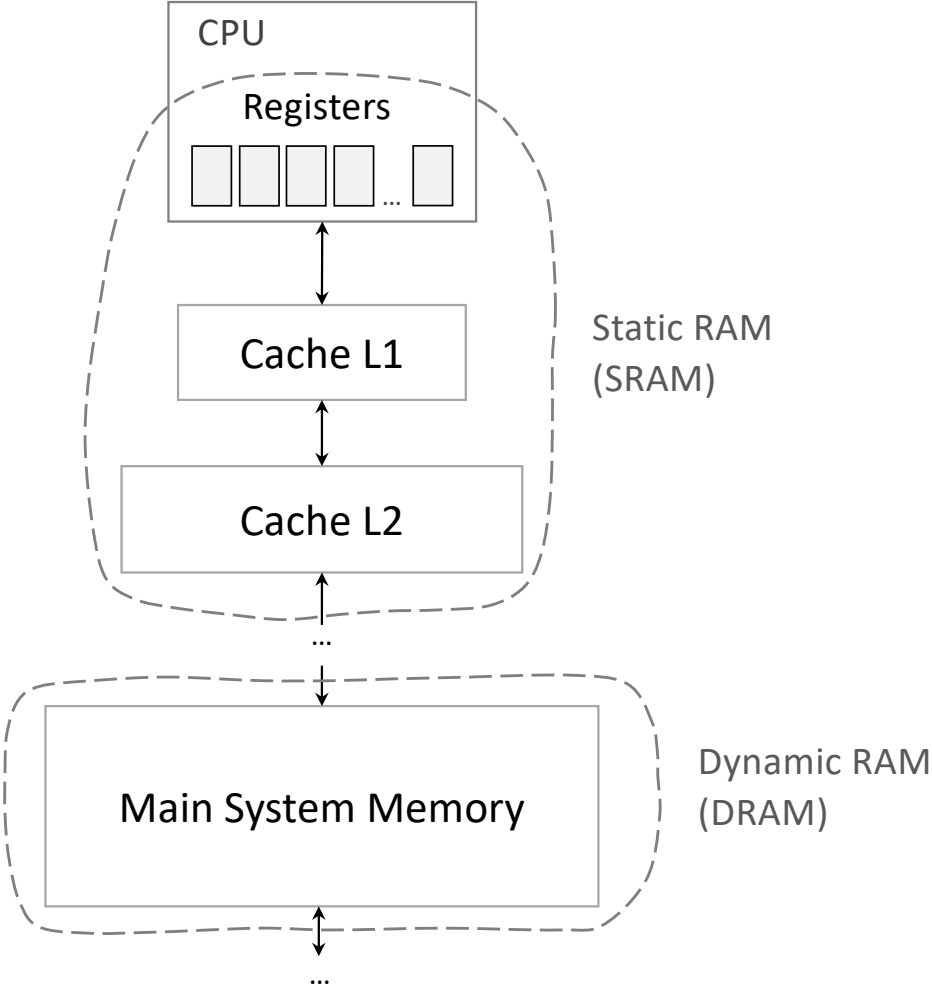
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The Comparison of DRAM and SRAM Memory Types



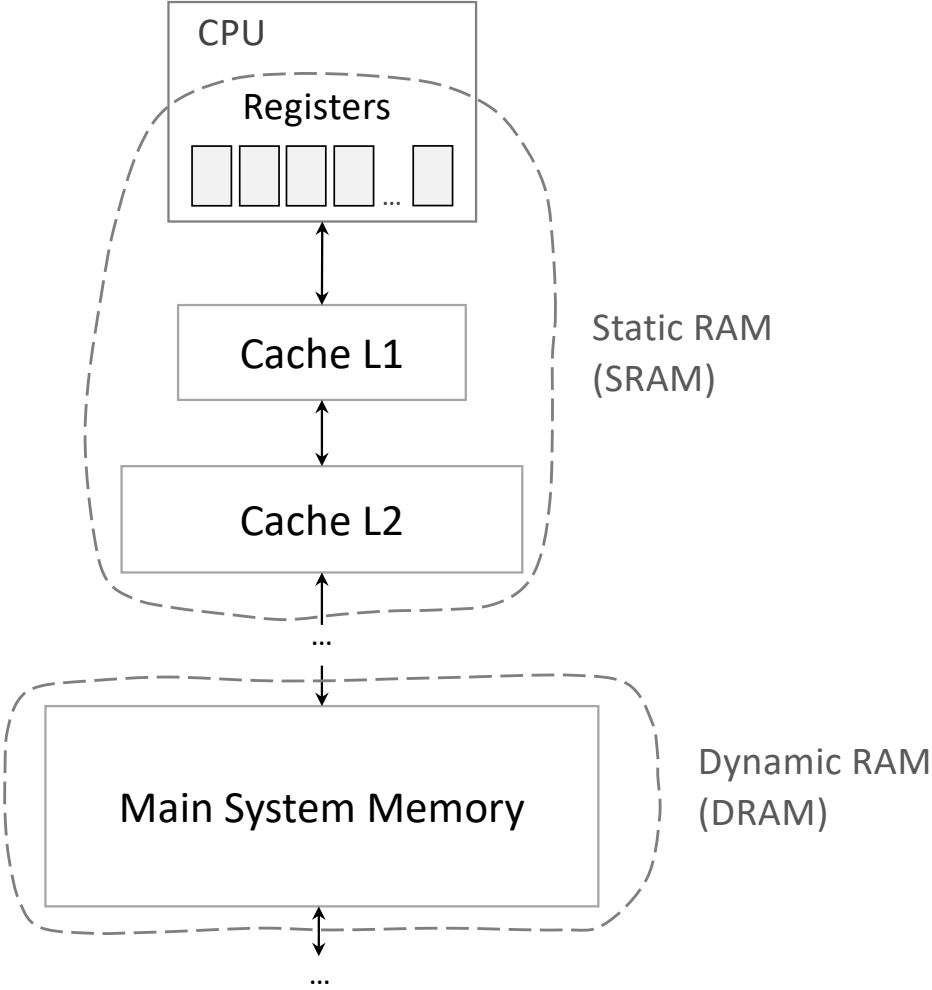
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Organisation	Complex	Simpler
Power Leakage		
Chip Reliability		
Volatility		
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



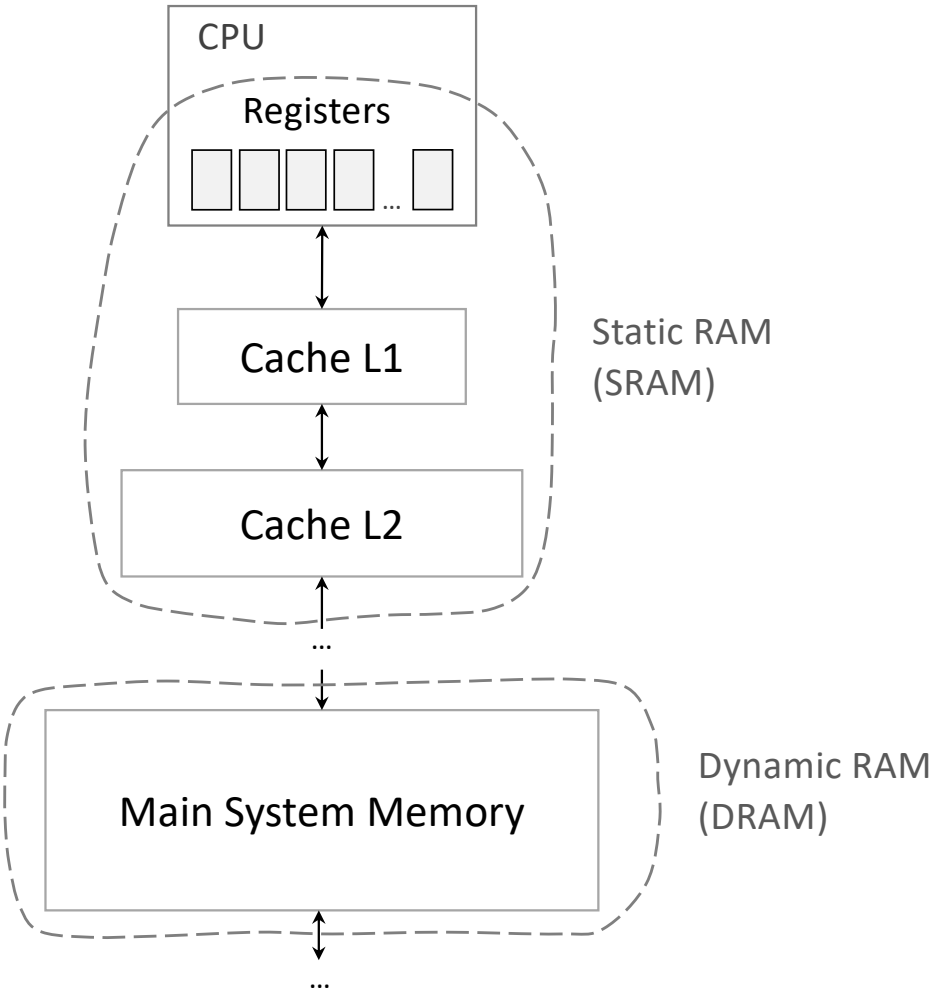
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Storage Element	Flip-flop	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption	Lower	Higher
Organisation	Complex	Simpler
Power Leakage	Not present	Significant
Chip Reliability		
Volatility		
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



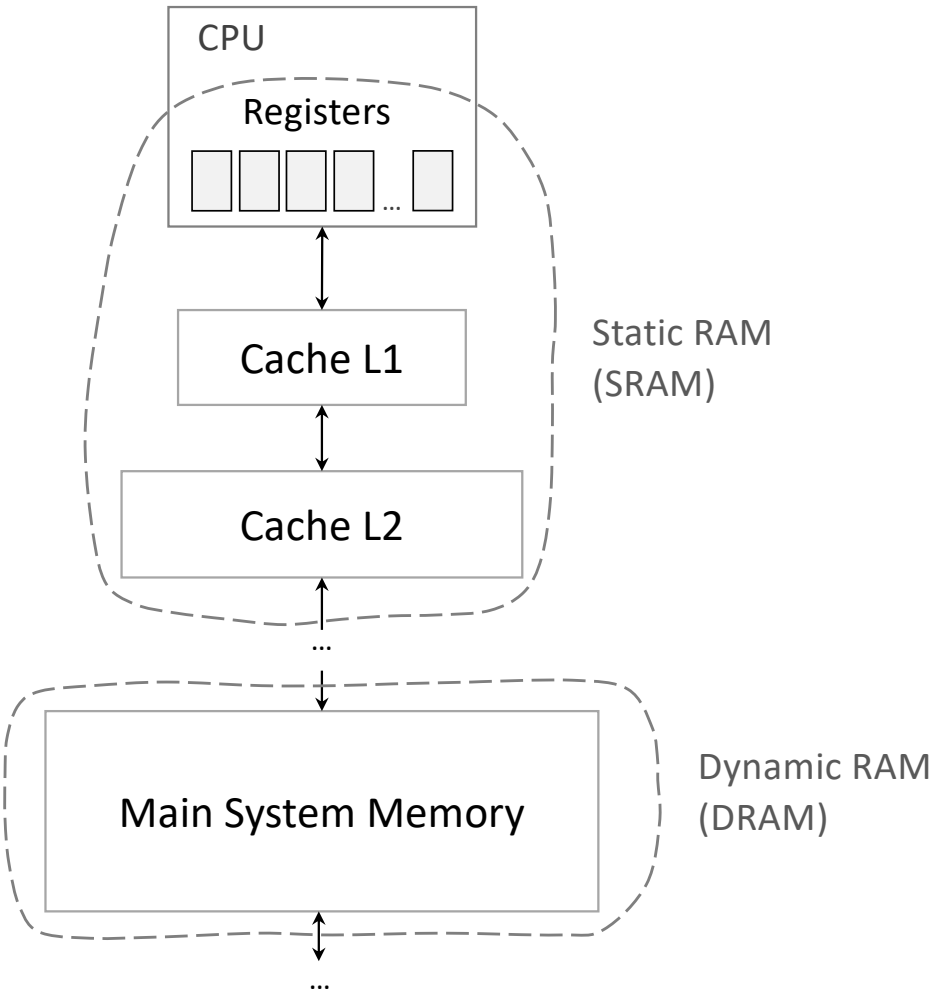
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Storage Element	Flip-flop	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption	Lower	Higher
Organisation	Complex	Simpler
Power Leakage	Not present	Significant
Chip Reliability	More reliable	Less reliable
Volatility		
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



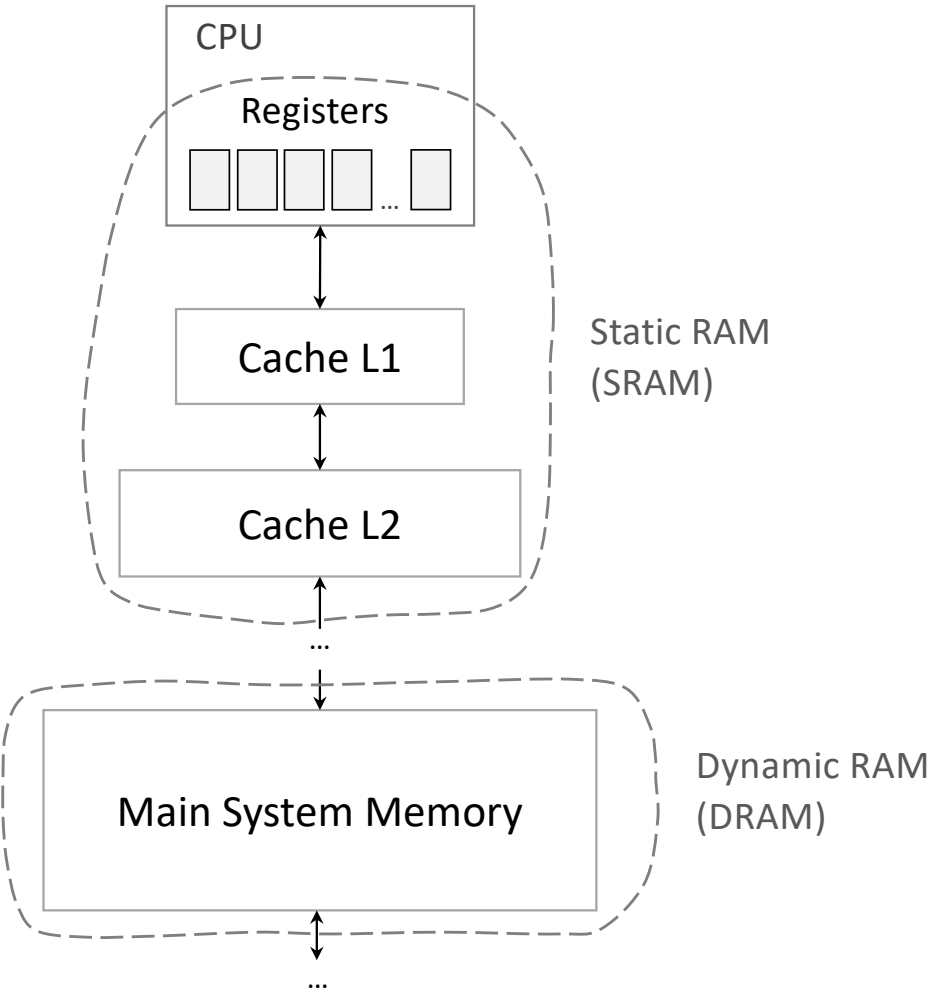
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Storage Element	Flip-flop	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption	Lower	Higher
Organisation	Complex	Simpler
Power Leakage	Not present	Significant
Chip Reliability	More reliable	Less reliable
Volatility	Both are volatile (lose data if power is off)	
Memory Cell Access		

The Comparison of DRAM and SRAM Memory Types



Characteristic	SRAM	DRAM
Access Speed	Faster	Slower
Storage Capacity	Smaller	Larger
Storage Element	Flip-flop	Capacitor
Usage	CPU cache, registers	System memory
Cost	Expensive	Cheaper
Power Consumption	Lower	Higher
Organisation	Complex	Simpler
Power Leakage	Not present	Significant
Chip Reliability	More reliable	Less reliable
Volatility	Both are volatile (require electrical power to keep data)	
Memory Cell Access	Each cell is accessed directly, unlike Sequential Access Memory (SAM)	

The Comparison of DRAM and SRAM Memory Types



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